

# The ASDBLR and DTMROC Detector Mounted Readout for the ATLAS TRT

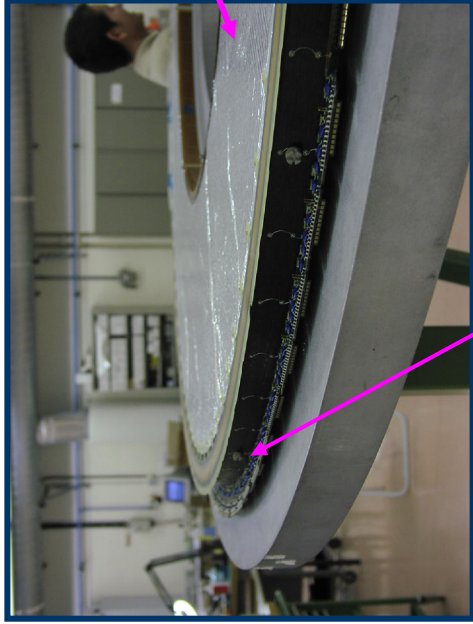
**Mitch Newcomer** for the ATLAS TRT Electronics Group

July 2, 2003

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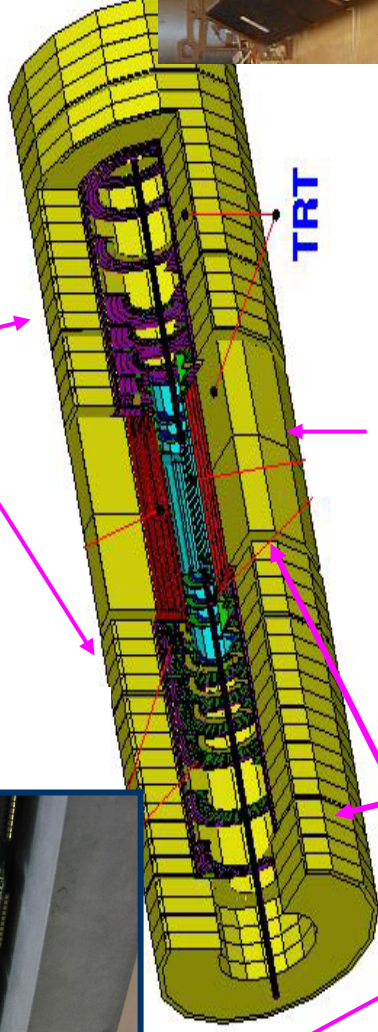
# TRT

# ATLAS TRT FEE2003



TRT Wheels

Radially Aligned Straws (320K channels)

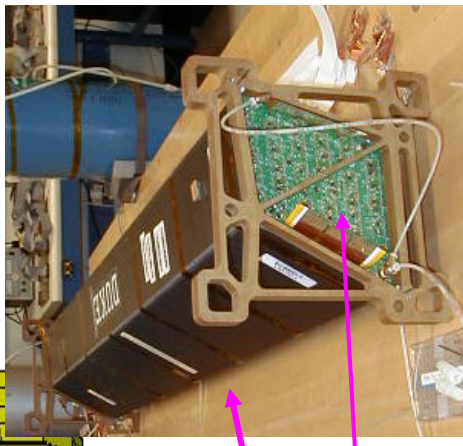


TRT

Barrel Modules

Axially aligned 100K channels

TRT Front End  
Electronics



# Detector Mounted Readout Objectives

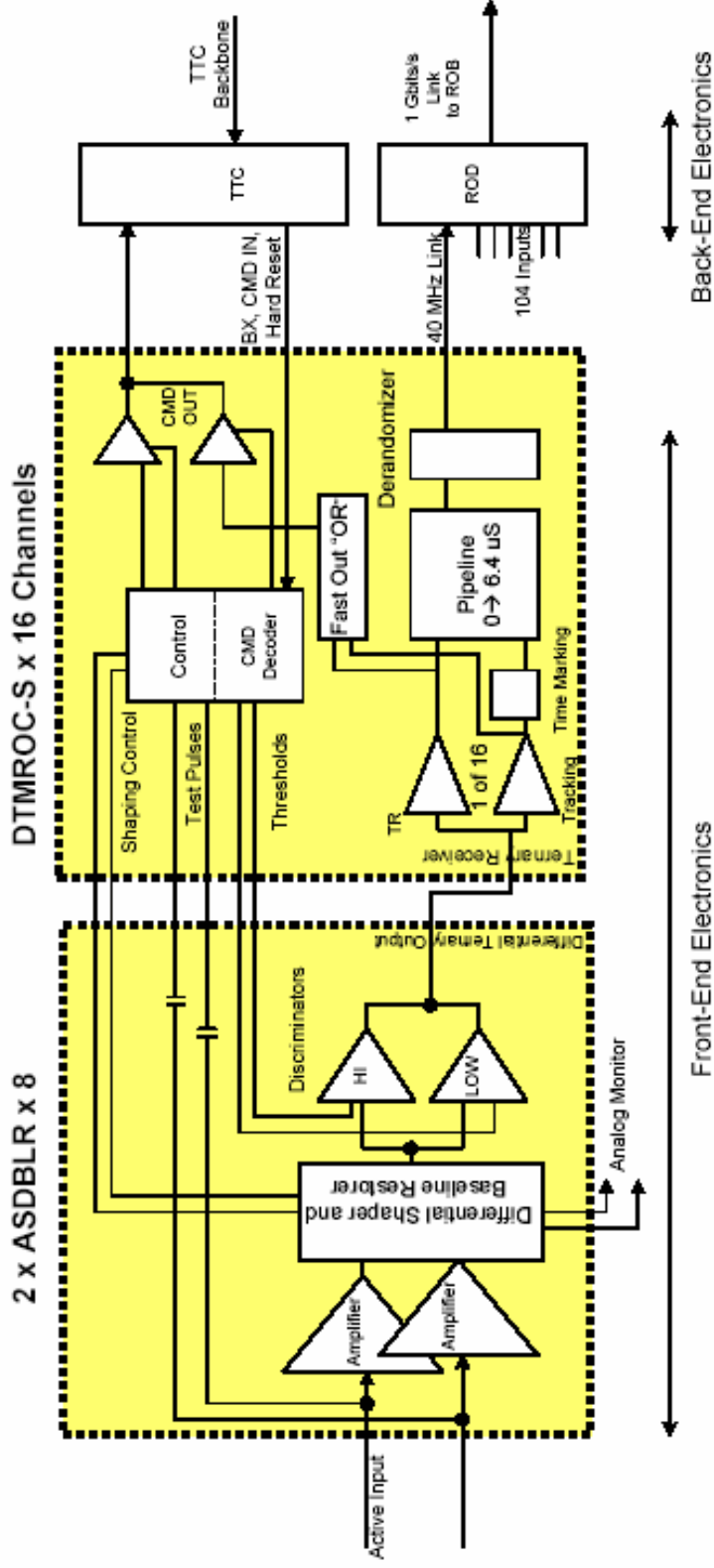
**ATLAS TRT**  
**FEE2003**

- Low Noise/Low threshold operation → ~2000e ENC  
    < 300KHz spontaneous straw tube trigger rate
- 1ns time resolution → ~130 $\mu$ m position resolution
- High Rate operation → 20MHz with stable threshold  
    (100:1 Signal variation)
- Radiation Tolerance → 3.5X10<sup>14</sup> n/cm 5MRad
- Reliable operation of high bandwidth Analog and Digital  
    readout ASICs without interference
- ATLAS R<sub>ead</sub> O<sub>ut</sub> D<sub>river</sub> Compatibility

# Readout Electronics basic block

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## 16 channel custom ASIC triplet



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# ASDBLR References

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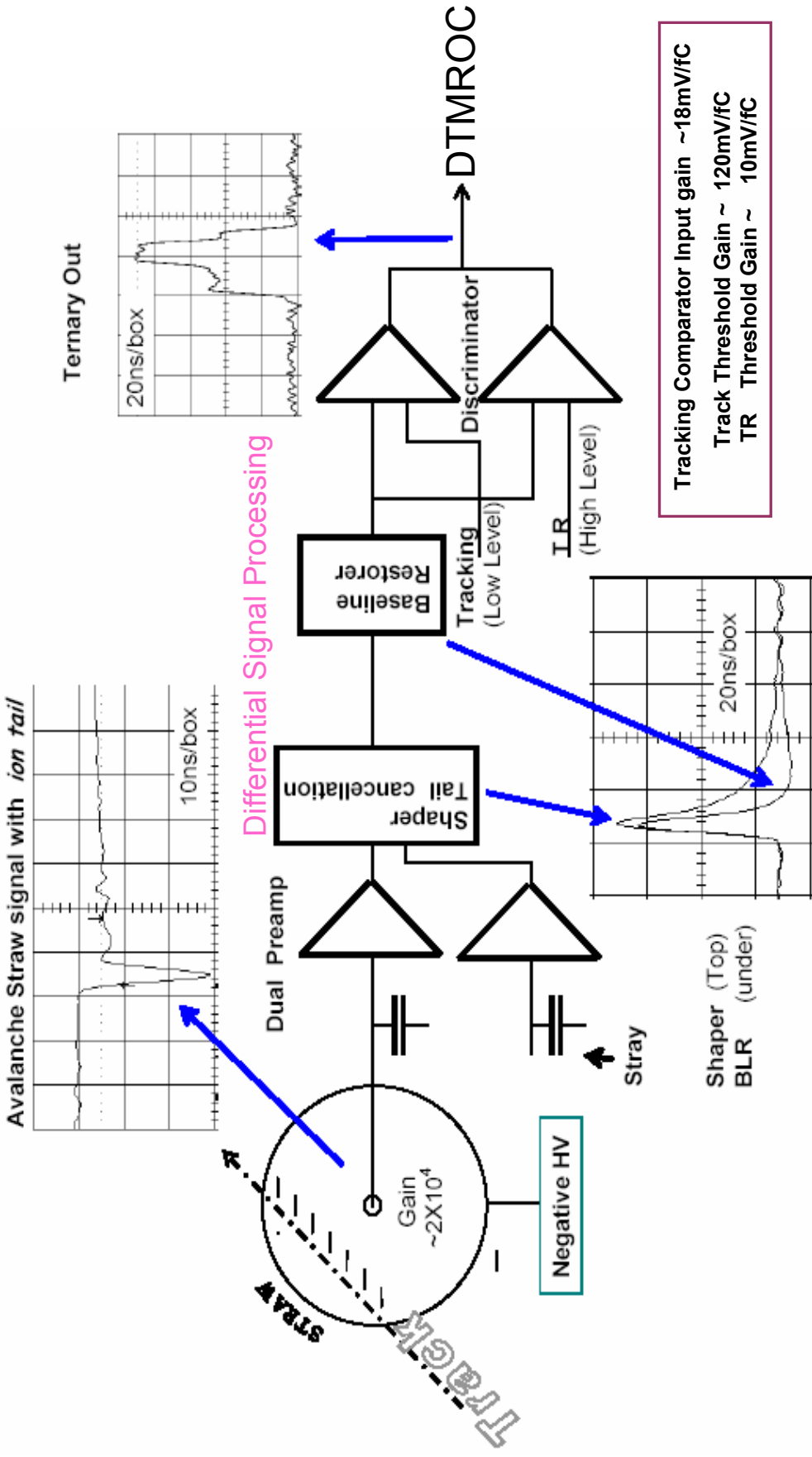
## **Implementation of the ASDBLR Straw Tube Readout ASIC in DMILL Technology**

N. Dressnandt, N. Lam, F.M. Newcomer, R. Van Berg and H.H. Williams  
*IEEE (2000) Trans. On Nucl. Sci. V48 n4 p1239*

## **An Amplifier-Shaper-Discriminator with Baseline Restoration for the ATLAS Transition Radiation Tracker**

B. Bevensee, F.M. Newcomer, R. P. Van Berg and H.H. Williams  
*IEEE (1996) Trans. on Nuc. Sci. V 43 p1725*

<http://www.hep.upenn.edu/atlas>



# ASDBLR Basic Design Spec

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- Power ~ 40mW/ch.
- Preamp Input protection ~ 2.8mJ.
- Analog Gain ~ 18mV/fC at Comparator input.
- Double Pulse Resolution ~ 25 - 50ns dependent on 1<sup>st</sup> pulse amplitude.
- Spontaneous Trigger Rate at 2fC threshold ~ 300KHz.
- High Threshold Maximum Range → 140fC.
- Ternary (comparator) output levels (nominal Design):

Signal	Tern Pos	Tern Neg
Quiescent	-400uA	0uA
Track only	-200uA	-200uA
Track & TR	0uA	-400uA

# ASDBLR Implementation

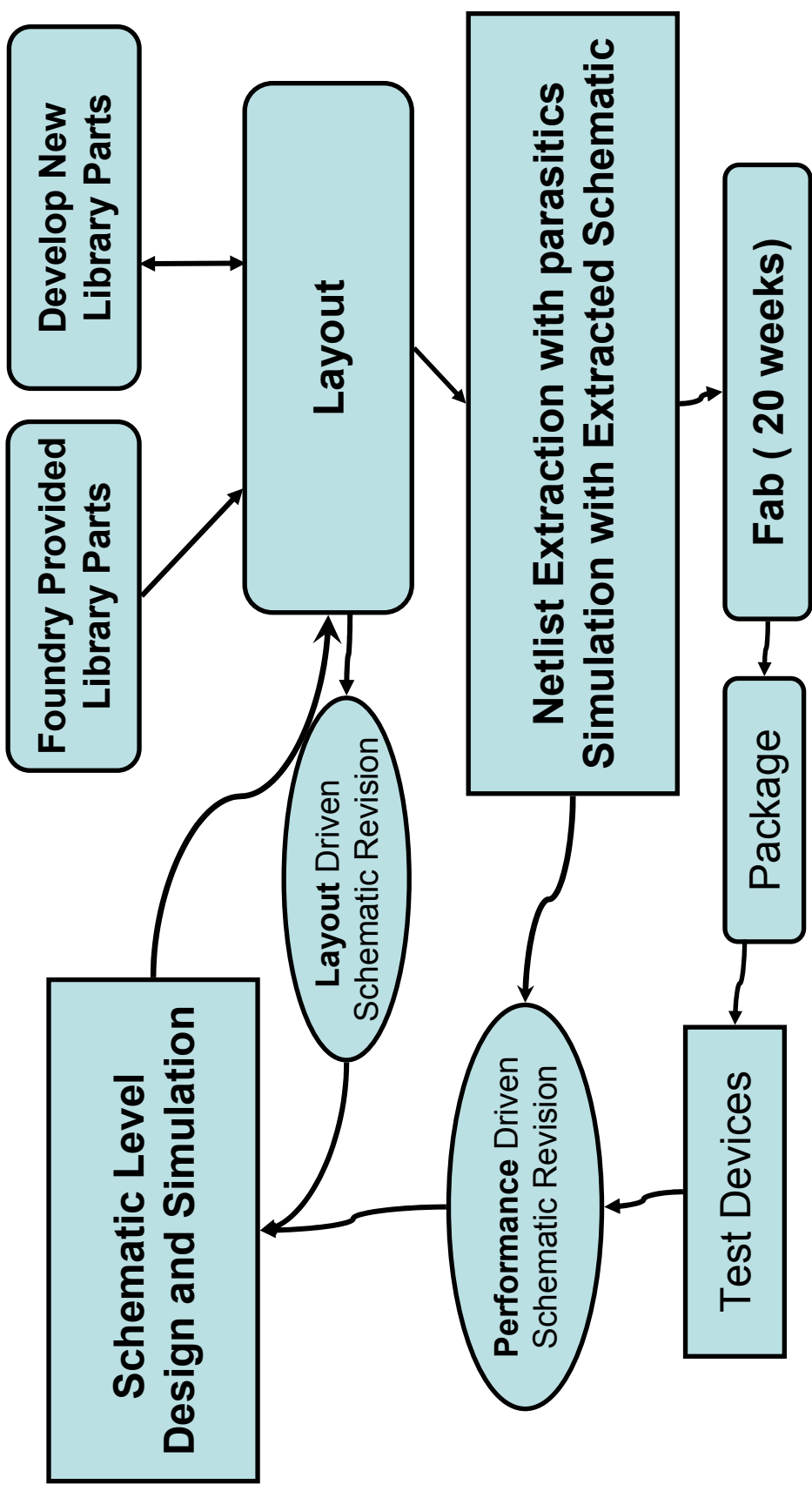
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- Process - Rad Tolerant 0.8um BiCMOS Technology (DMILL)
- Designed at the discrete device level using SPICE for Simulation
- Channel Complexity 160 Bipolar Transistors / 10 CMOS Switches  
160 Resistors / 105 Capacitors
- Channel based Layout ~
  - Avoided metal runs over transistors/resistors.
  - Double vias where possible.
  - Separated Analog and Comparator/Ternary Driver Power
  - Dedicated power bus distribution at the channel level.
  - Substrate Contact and Power buss isolation between ch.
  - Preamp Supply filter on each channel.
- Eight (nearly) identical Channels on 340um Pitch



# ASDBLR design Cycle

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# ASDBLR02 Final Design

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## Final Design Improvements

- Reduce area of input protection network → Reduce Capacitance 11pf → 5pf.
- Increase Input transistor current to 7.5uA/m reduce beta loss.
- Increase analog gain by 50% to reduce sensitivity to device matching in comparator. (56mV/fC at BLR output)

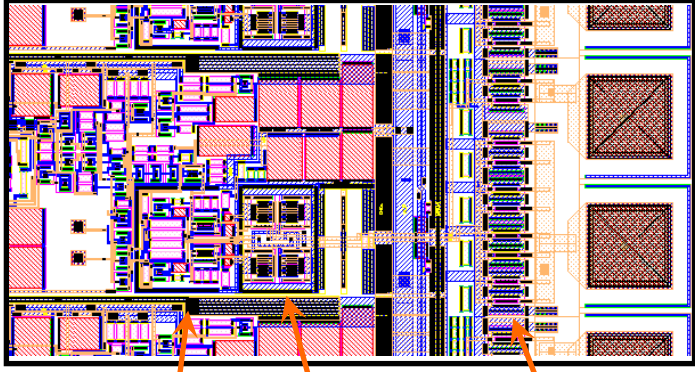
## Measured Results

- Input referred threshold matching good, RMS < .25fC
- Noise ~ 2100e ENC on board with ~5pF capacitance (100e/pf).
- Power ~ 40mW/channel.
- High Rate operation ~ demonstrated to 20MHz (pulser tests)

# Production ASDBLR

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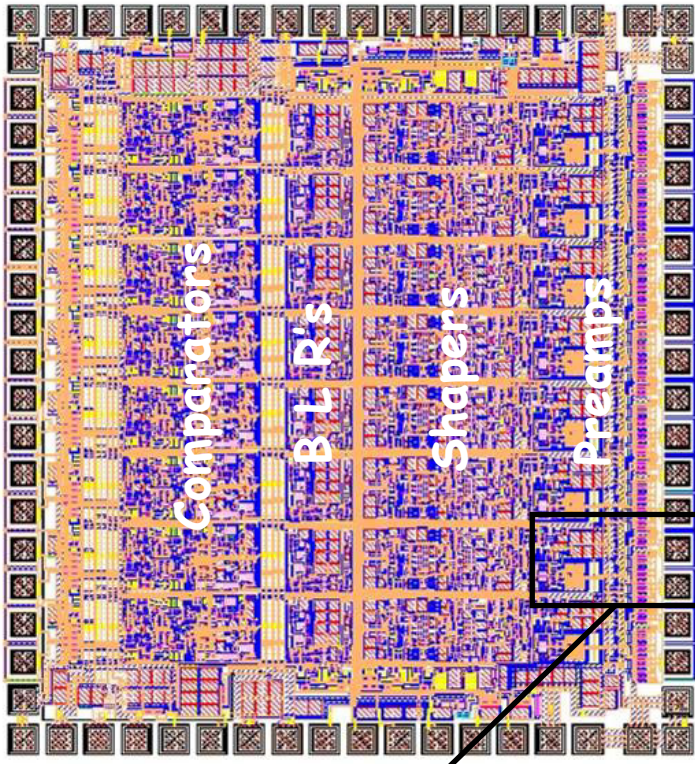
3.3 X 3.6mm



Dual Preamps  
intermingled  
layout

Input  
Transistors in  
cross Quad  
Configuration

Input protection NPN  
Transistors  
Expanded Geometry  
Emitter Stripes 4 x 30 um



Comparators

B L R's

Shapers

Preamps

# ASDBLR Radiation Testing

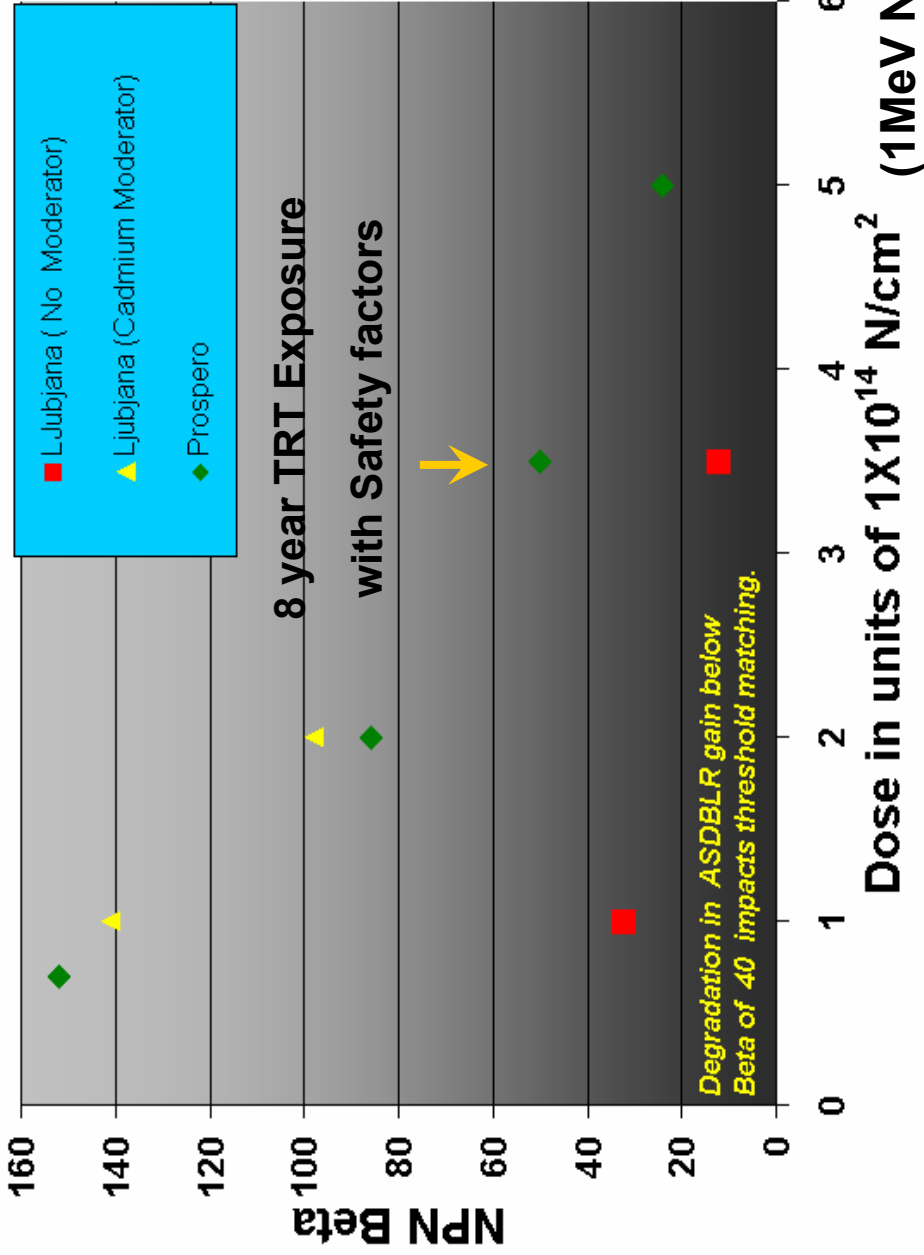
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- **Gamma Testing up to 7MRad with no significant performance degradation.**
- **1MeV NEIL Neutron Testing to  $5 \times 10^{14}$  (10 year with safety factor) shows a significant reduction in beta resulting in lower gain and increasing the channel to channel threshold offset. At Beta = 30 the gain is lowered by ~ 50%.**
- **DMILL NPN Beta is sensitive to Thermal Neutrons**  
**More study needed. Moderator re-evaluation?**

# Neutrons

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## DMILL NPN Neutron Sensitivity



Thermal Neutrons present at the Ljubjana facility point out a possible weakness using the DMILL Process.

Careful comparison of these results with the expected exposure in the ATLAS ID need to be performed.

*All devices annealed at 150° C for 48 hrs.*

# ASDBLR Radiation Testing ATLAS TRT report NSS 2002 FEE2003

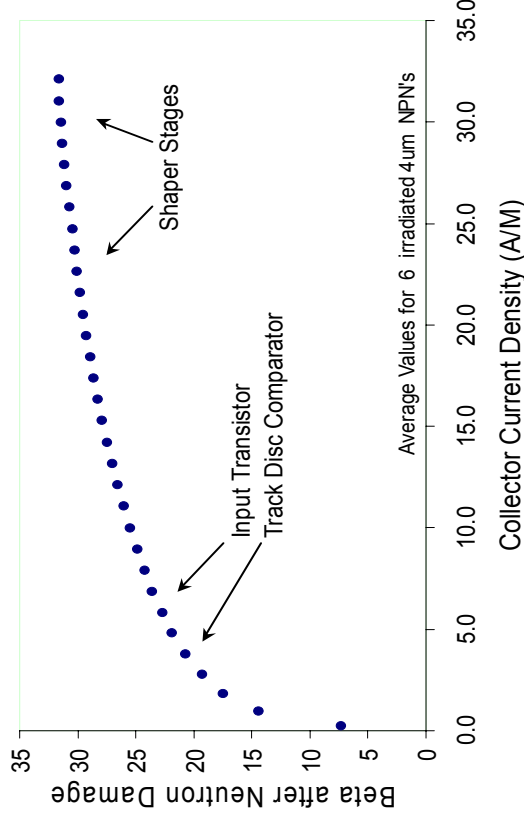
## Summary of Device tests to 11 / 2002

ASDBLR	# chips	Power on	Date	Type Dose <sup>1</sup>	Change in Resistance	Post Rad NPN Beta
99	3		4/00	5X10 <sup>13</sup> n	NA	84
	3		4/00	1X10 <sup>14</sup> n	NA	52
00	6	x	5/01	5Mrad $\gamma$	5%	180
	9		10/01	3.5 X10 <sup>14</sup> n	1.5%	55 <sup>3</sup>
01	6	x	6/02	1.5X10 <sup>14</sup> p	5%	70
01	16	x	7/02	7MRad $\gamma$	8%	130
01	10		5/02	3.5X10 <sup>14</sup> n	10.4%	11 <sup>2,3</sup>

<sup>1</sup> n and p dose is in units of particles/cm<sup>2</sup>.

<sup>2</sup> Thermal neutron dose high  $\sim 10^{14}$  n/cm<sup>2</sup>.

<sup>3</sup> After annealing [23hrs@150C](mailto:23hrs@150C)



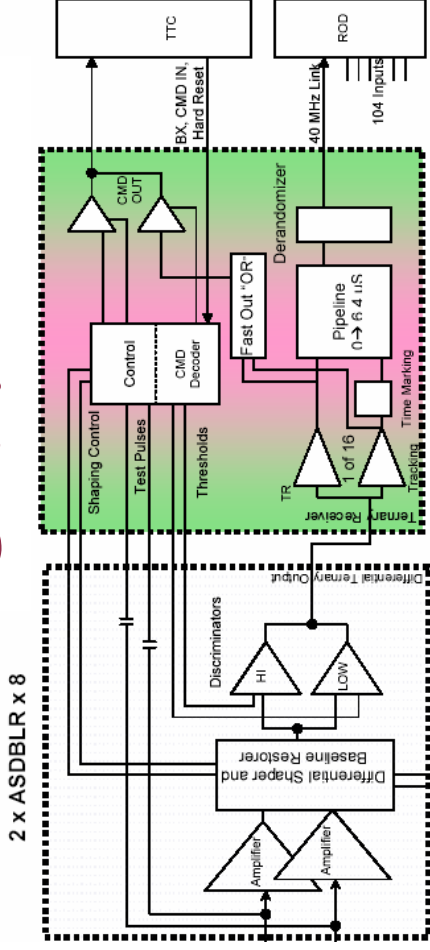
The measured current gain of DMILL NPN transistors after exposure to 3.5X10<sup>14</sup>n/cm<sup>2</sup> and prior to annealing. The arrows show the operating points chosen for various parts of the ASDBLR channel design. After annealing the beta increased by a factor of two.

**From: Radiation Hardness: Design Approach and Measurements of the ASDBLR ASIC for the ATLAS TRT**  
*Nandor Dressnandt, Mitch Newcomer, member IEEE, Ole Rohne and Steven Passmore*

**See NSS 2002 Conference Record**



## DTMROC-S



## CERN MicroElectronics and Penn

V.Rylov

JINR, Moscow, Russia and University of Lund, Lund, Sweden

**F.Anghinolfi, Ph.Farthouat, P.Lichard**

CERN, Geneva 23, Switzerland

**R.Szczygiel**

CERN, Geneva 23, Switzerland and INP, Cracow, Poland

**N.Dressnandt, P.T.Keener, F.M.Newcomer, R.Van Berg,**

**H.H.Williams**

University of Pennsylvania, Philadelphia, USA

# DTMROC References

**ATLAS TRT**  
**FEE2003**

## ***Implementation of the DTMROC-S ASIC for the ATLAS TRT Detector in a 0.25 $\mu$ m CMOS technology***

***V.Ryjov, F.Anghinolfi, Ph.Farthouat, P.Lichard, R.Szczygiel, N.Dressnandt, P.T.Keener,  
F.M.Newcomer, R.Van Berg, H.H.Williams, T.Akesson, P.Eerola***

***NSS 2002 Conference Record***

## ***Progress in the Development of the DTMROC Time Measurement Chip for the ATLAS Transition Radiation Tracker (TRT)***

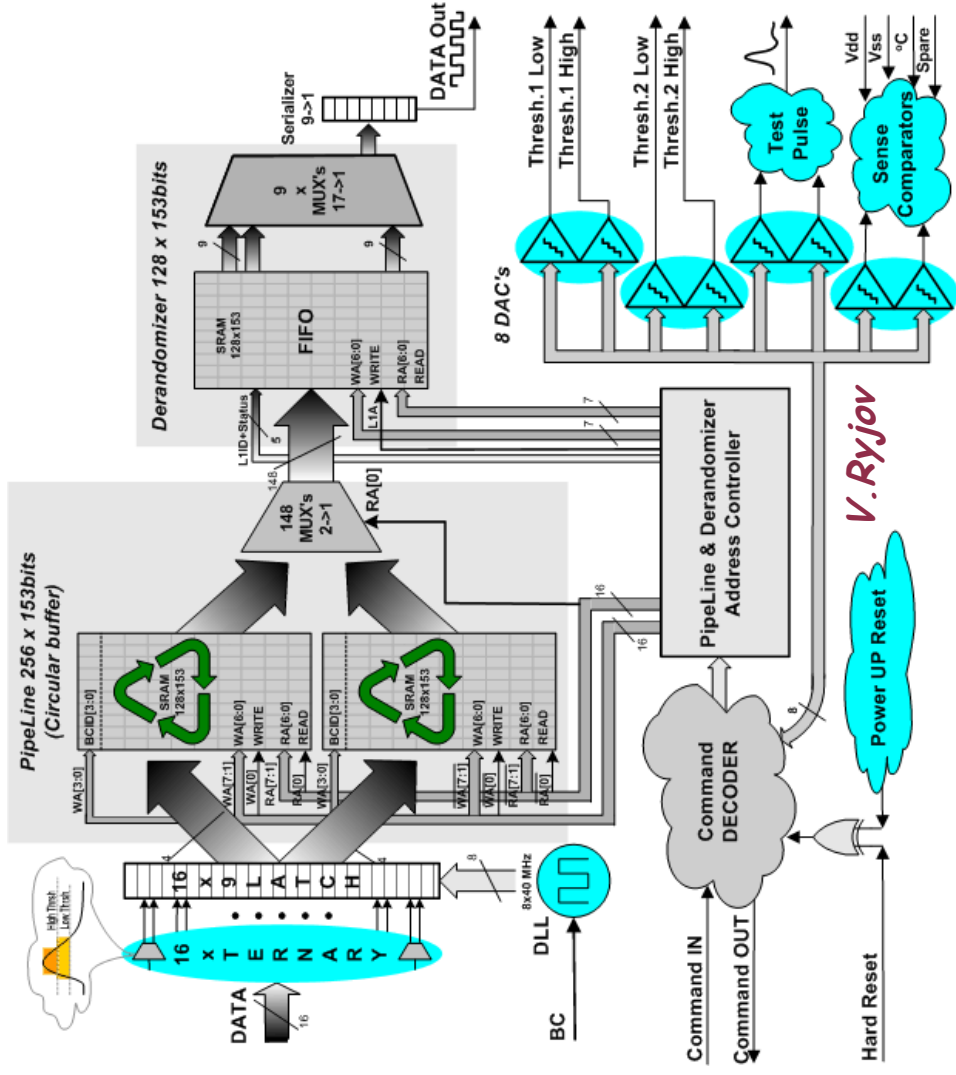
***C. Alexander, F. Anghinolfi, N. Dressnandt,  
T. Ekenberg, Ph. Farthouat, P. T. Keener, N. Lam, D. La Marra,  
J. Mann, F. M. Newcomer, V. Ryjov, M. Soderberg, R. Szczygiel,  
V. Tikhomiro, R. Van Berg, H.H. Williams.***

***IEEE (2000) Trans. On Nucl. Sci. V48 n3 p514***

***<http://hep.upenn.edu/atlas>***



## functional Blocks

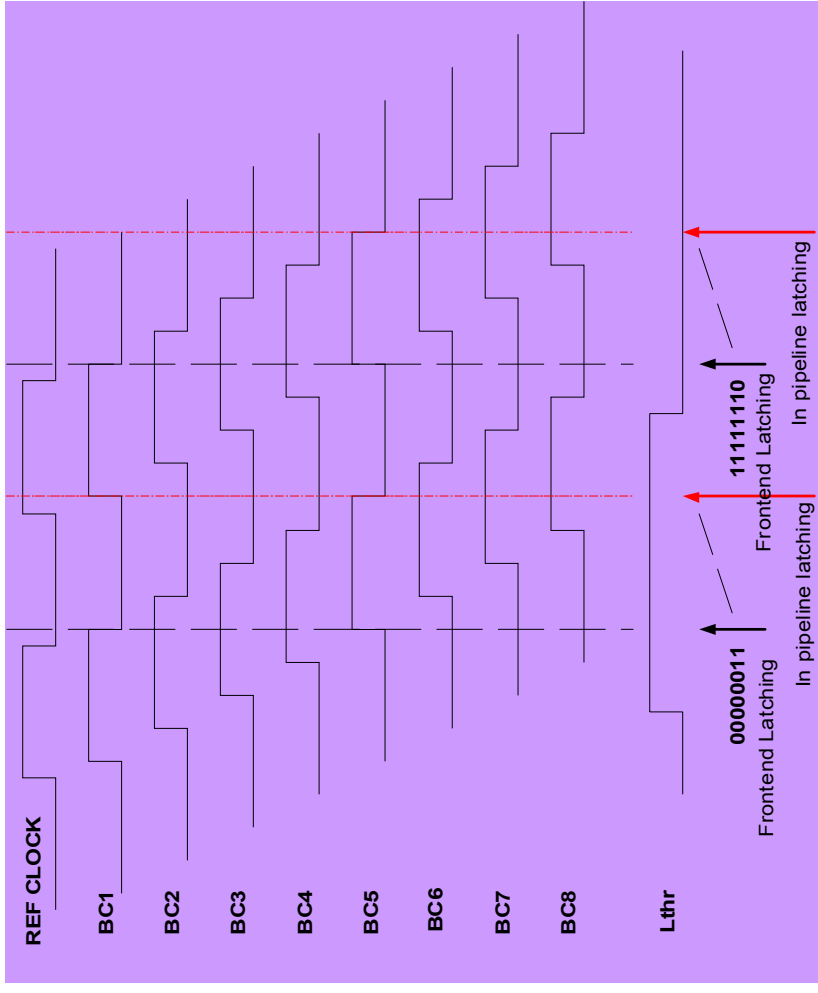


V. Ryjov

### *32 elements delay chain, phase detector, charge pump*

40MHz Clock  $\rightarrow$  3ns time bins

- 8 equally spaced clock outputs used to sample straw track pulses
- 50% duty cycle clock regenerated to run the chip core logic

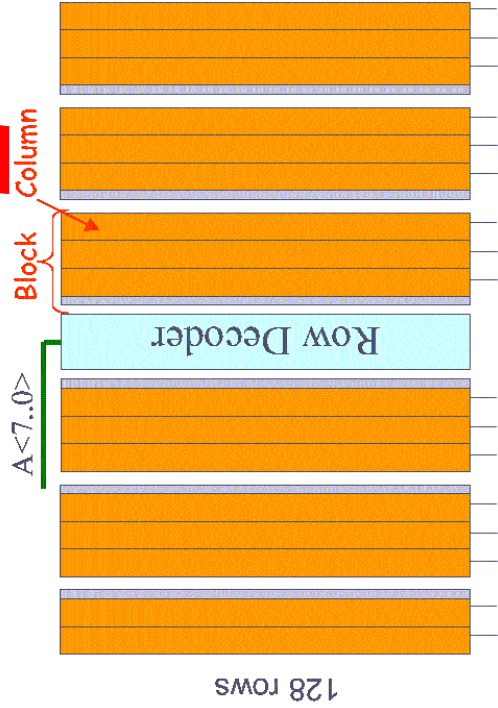


# DTMROC-S

## Memory / Pipeline

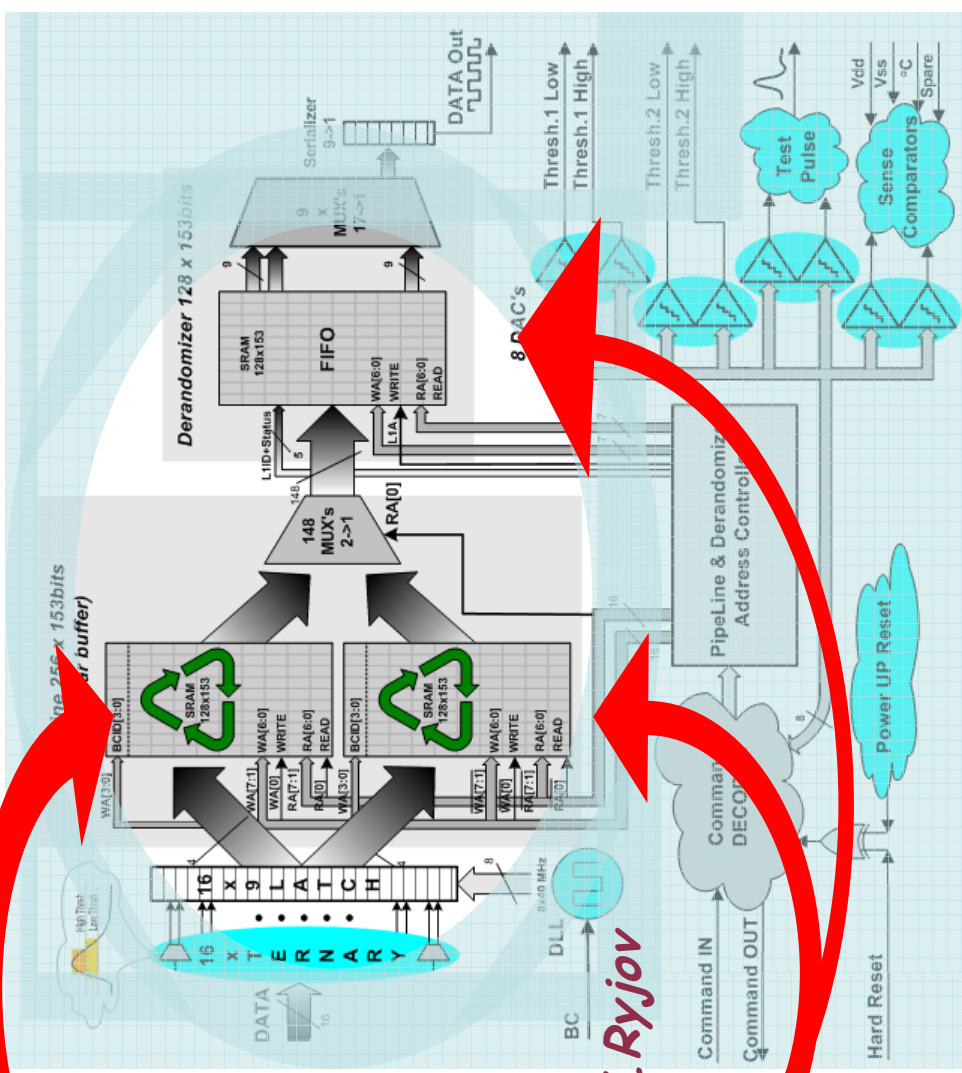
# ATLAS TRT

# FEE2003



V. Ryjov

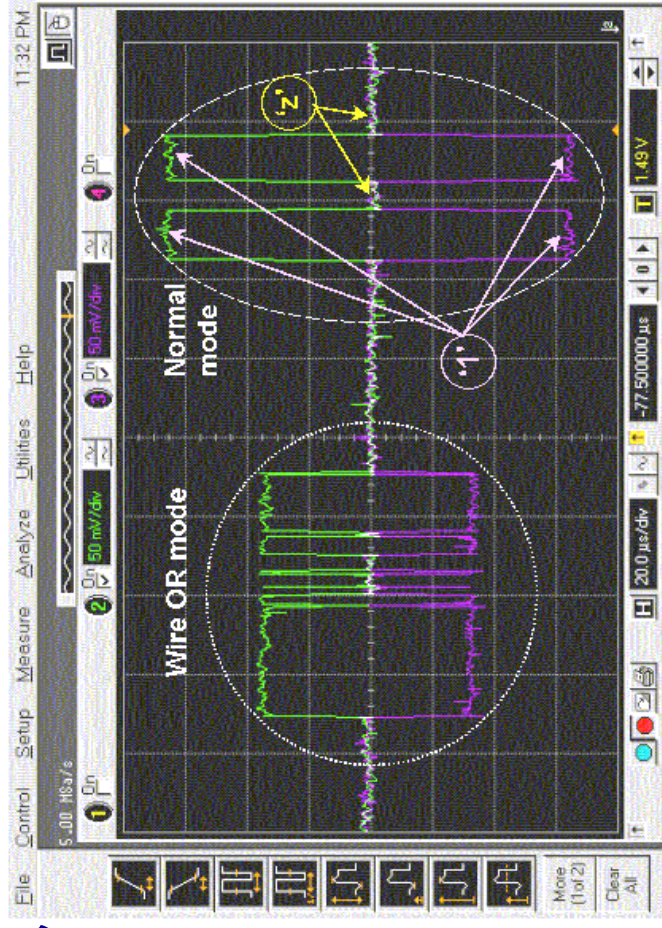
Dual-port 128x153-bit SRAM  
(2.39KB)



# DTMROC-S I/O

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- Full/Reduced read-out : 444/380 bits per event, including Header
- LVDS-compatible, tristate drivers -> 40 Mbits/s copper links
- "Wire-OR" - for self triggering fast-out option - selected ternary inputs contribute to the chip-level trigger
- Up to 15 DTMROCs can be "OR'ed on a common buss

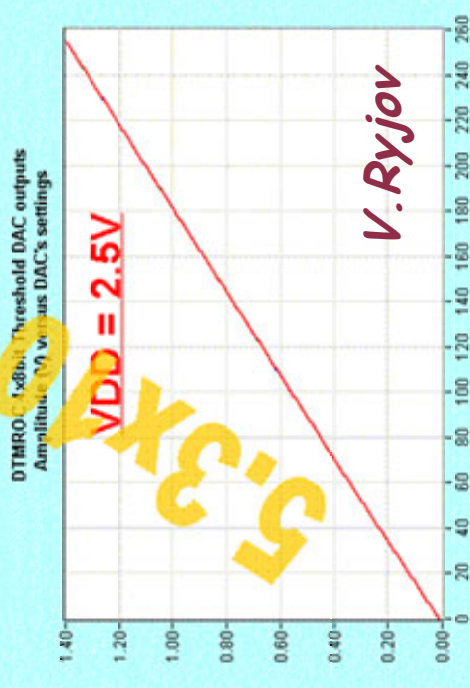
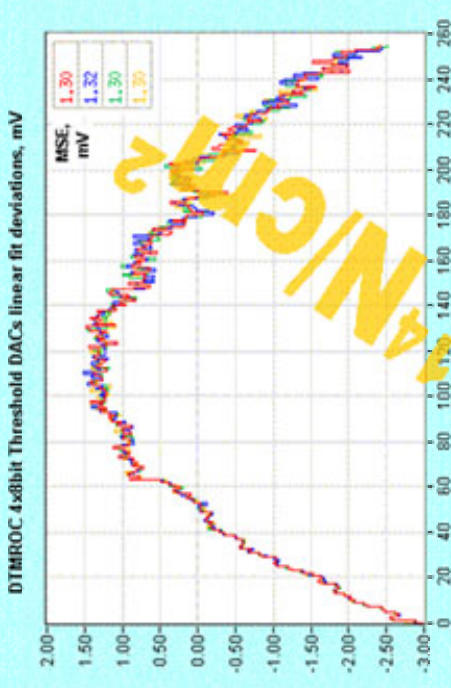
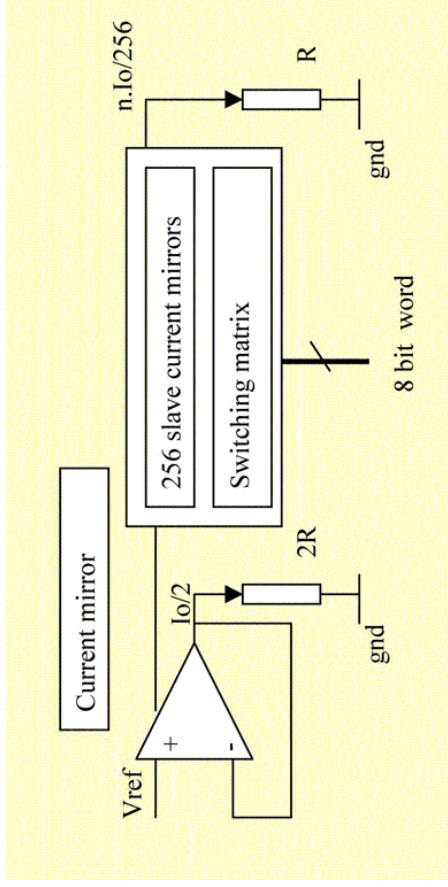




# DTMROC-S DAC's

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- Internal bandgap reference 1.26V
- Current mirror master - 128 PMOS unit devices ( $L=8\mu\text{m}$ ,  $W=5\mu\text{m}$ )
- 256 identical PMOS slave current mirrors per DAC

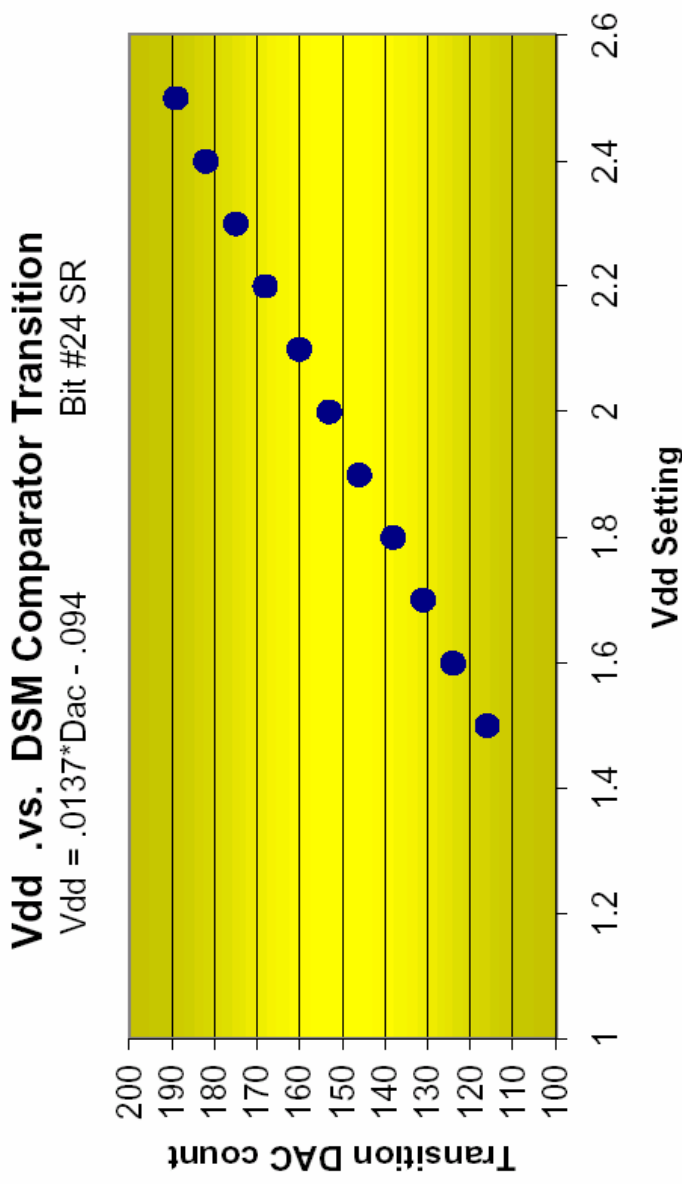


# DTMROC-S

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## Analog Sensing

- *Two DACs*
- *Four Comparators*
  - *Temperature*
  - *VDD*
  - *Ext Voltage 1*
  - *Ext Voltage 2*



*Vdd Sense remained at 191 from 26 - 55 C*

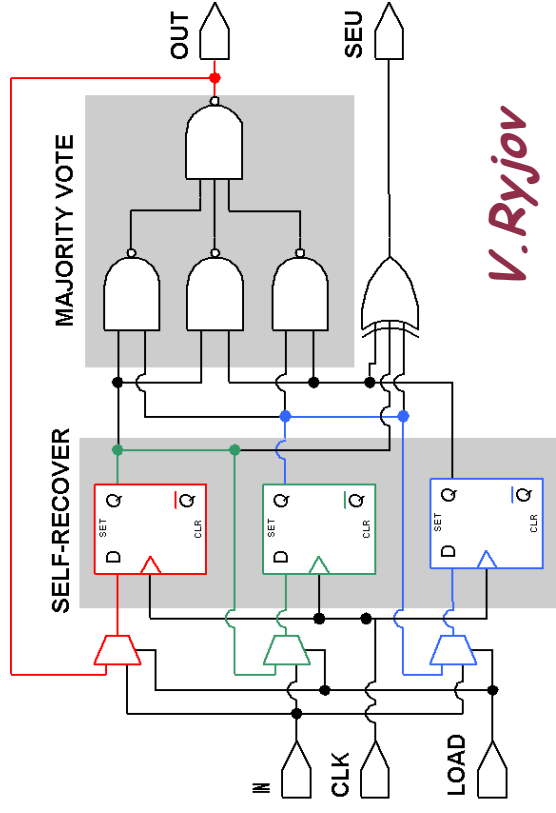
# DTMROC-S

## *testability*

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- *General-purpose 32-bits Status Register*
- *Logical OR of all DTMROC error indicators in the Data Header field*
- *Parity check logic for all internal registers*
- *Lock status, a "watch dog" and a "dynamic" check circuitries examine the DLL*
- *JTAG Boundary-Scan*
- *Special scan mode - configures all DTMROC flip-flops as a large shift register controlled via JTAG interface*
- *Memory Build-In-Self-Test (BIST) controlled via the Configuration register and JTAG interface*

- *Internal registers are equipped with parity error check*
- *The most critical parts are built of the SEU resistant and self-recovering elements based on triple logic with majority vote.*
- *Statistics circuit monitors the number of detected SEU's*

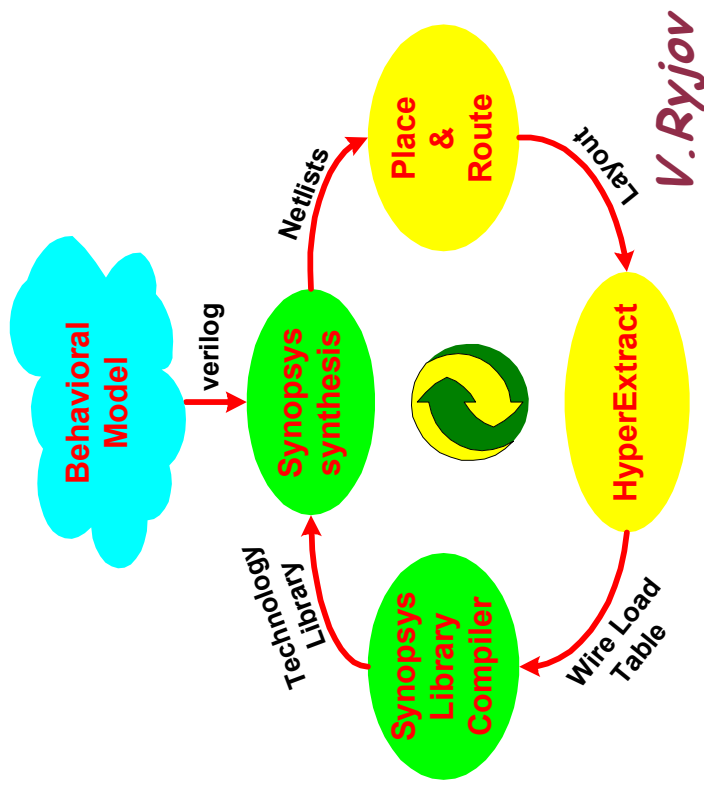




# DTMROC-S Design Tools (CERN based)

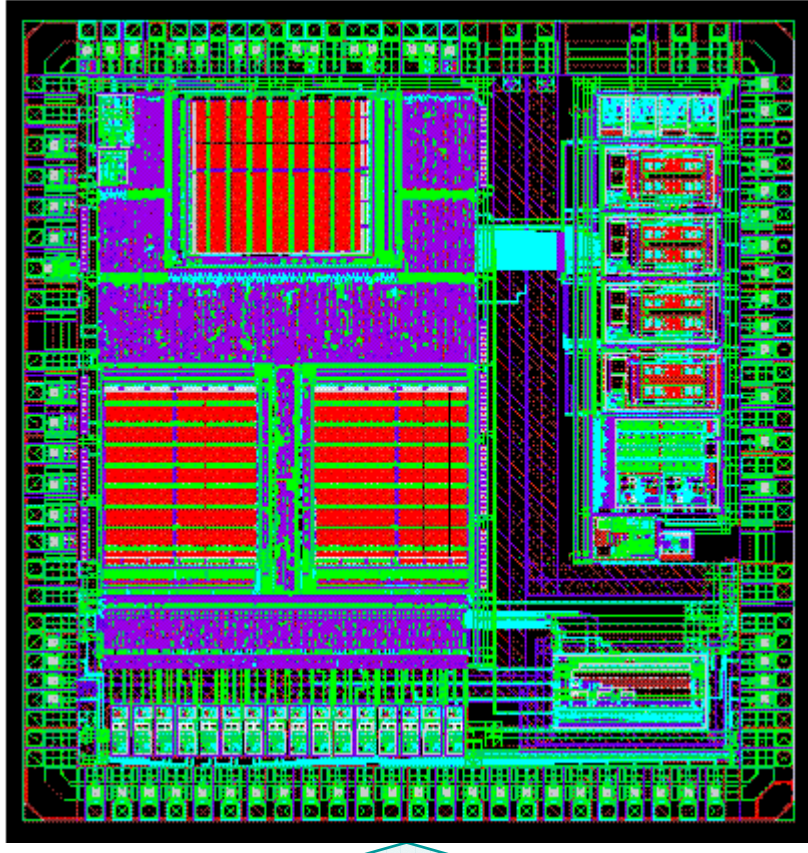
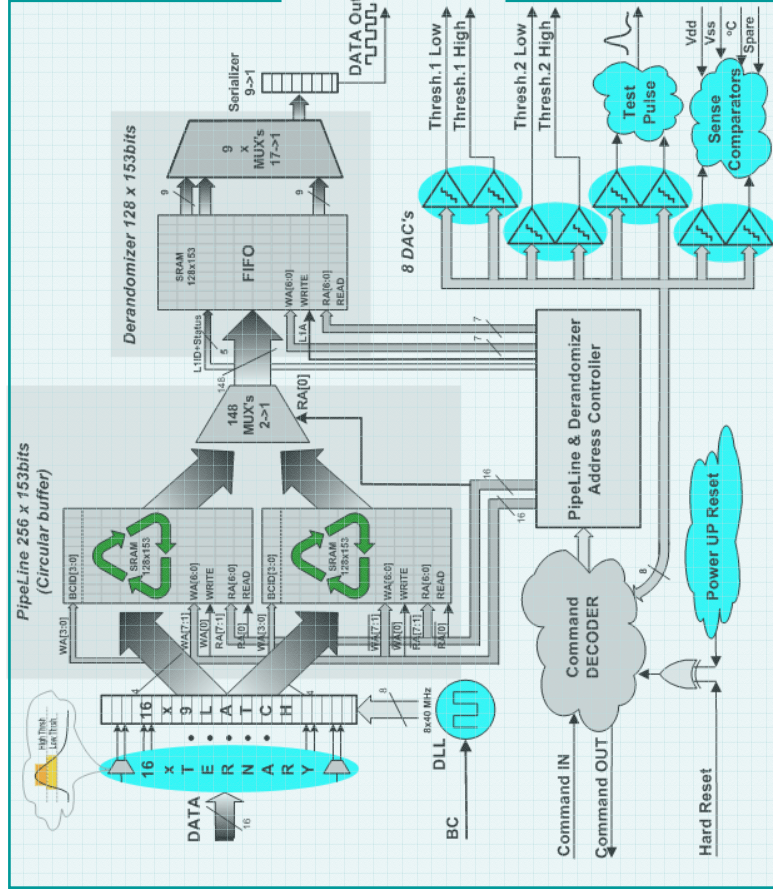
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- Verilog modelling
- Synopsys synthesis tools
- Silicon Ensemble Place&Route tools
- Completely scripted physical design flow
- Number of synthesis-layout cycles to predict post-route timing during RTL synthesis
- NC Verilog Simulator – Interleaved Native Compiled Code Architecture



# DTMROC-S Layout

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~500k Transistors

Die size 5.2x5.0 mm<sup>2</sup>

# DTMROC-S

## Fab

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- Submitted/fabricated (.25um process) in Jan 2002
  - Wafer size 8" (350 $\mu$ m)  $\rightarrow$  1017 useable dies per wafer
- 850 chips tested on the mixed signal IMS Tester at CERN
- 5 process corner (85/92/100/115/125%) evaluated
- 87% Yield for 850 chips
- Irradiation tolerance test at CEA Saclay Pagure facility in July 2002
- SEU sensitivity evaluated at the CERN PS in July 2002
- Test Beam at the CERN H8 in August-September 2002

## Radiation Testing

### Total Ionizing Dose tolerance

- Tested at CEA Saclay Pagure facility in July 2002
- 7 Mrad total dose / 1.33 MeV gamma radiation
- ~10% increase in the DAC's output voltage after irradiation, no DNL change
- No variations in the power consumption and the chip performance

### SEU sensitivity

- Evaluated at the CERN PS irradiation facility in July 2002
- Integrated fluence of  $1.8 \times 10^{14}$  p/cm<sup>2</sup> on 24 GeV beam
- SEU cross-section for a single D flip-flop in different internal registers varies from  $0.8 \times 10^{-14}$  to  $1.2 \times 10^{-14}$  cm<sup>2</sup>
- Impact of SEU's in the vital components is suppressed by self-recovering logic

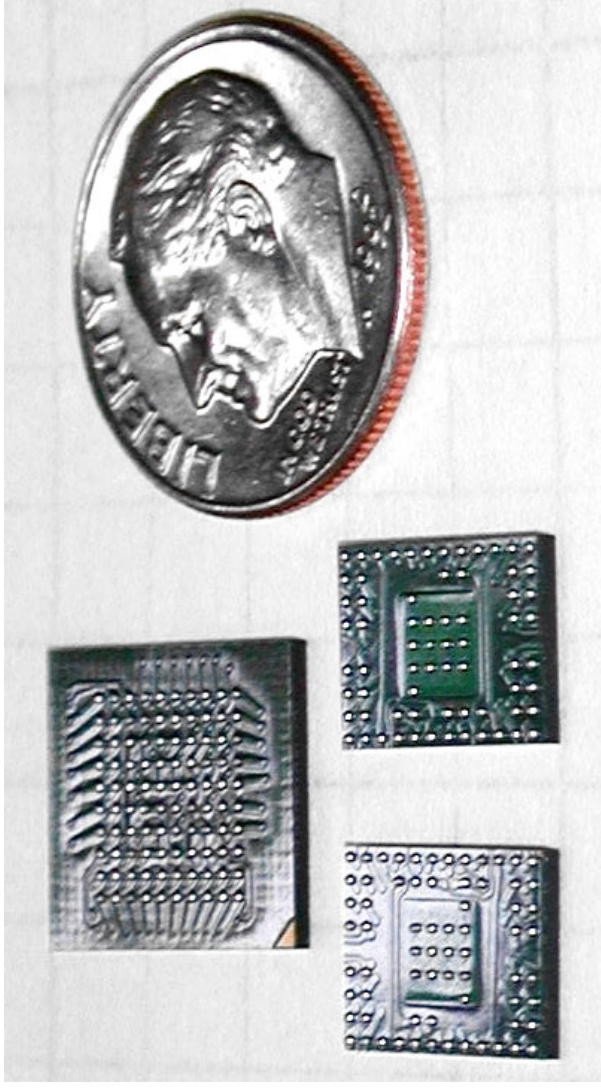


# ASDBLR & DTMROC Packaging Labeling

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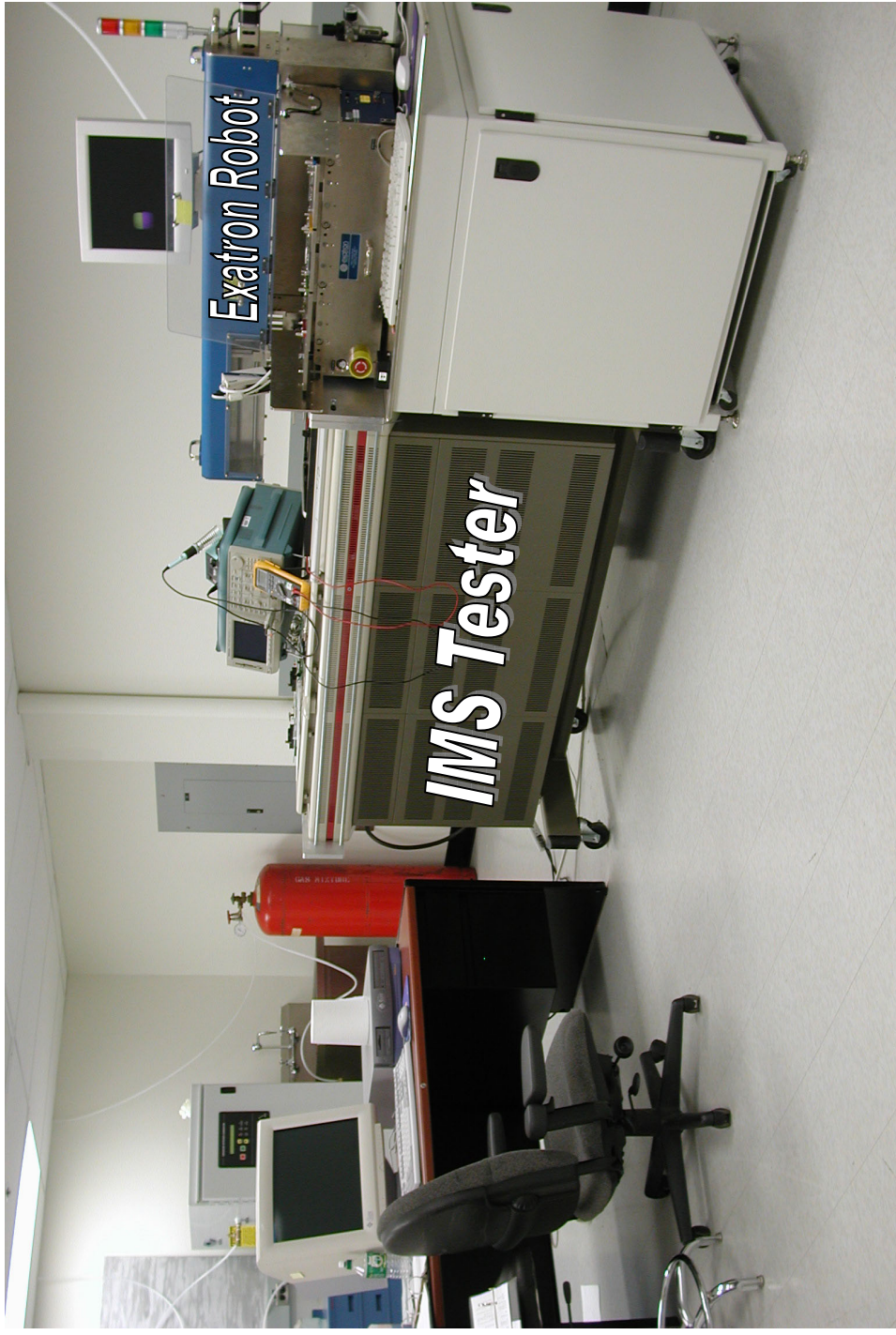
## Fine Pitch Ball Grid Arrays

Laser Marked packages  
2D Bar code  
Human Readable  
numbering



# ASIC Testing

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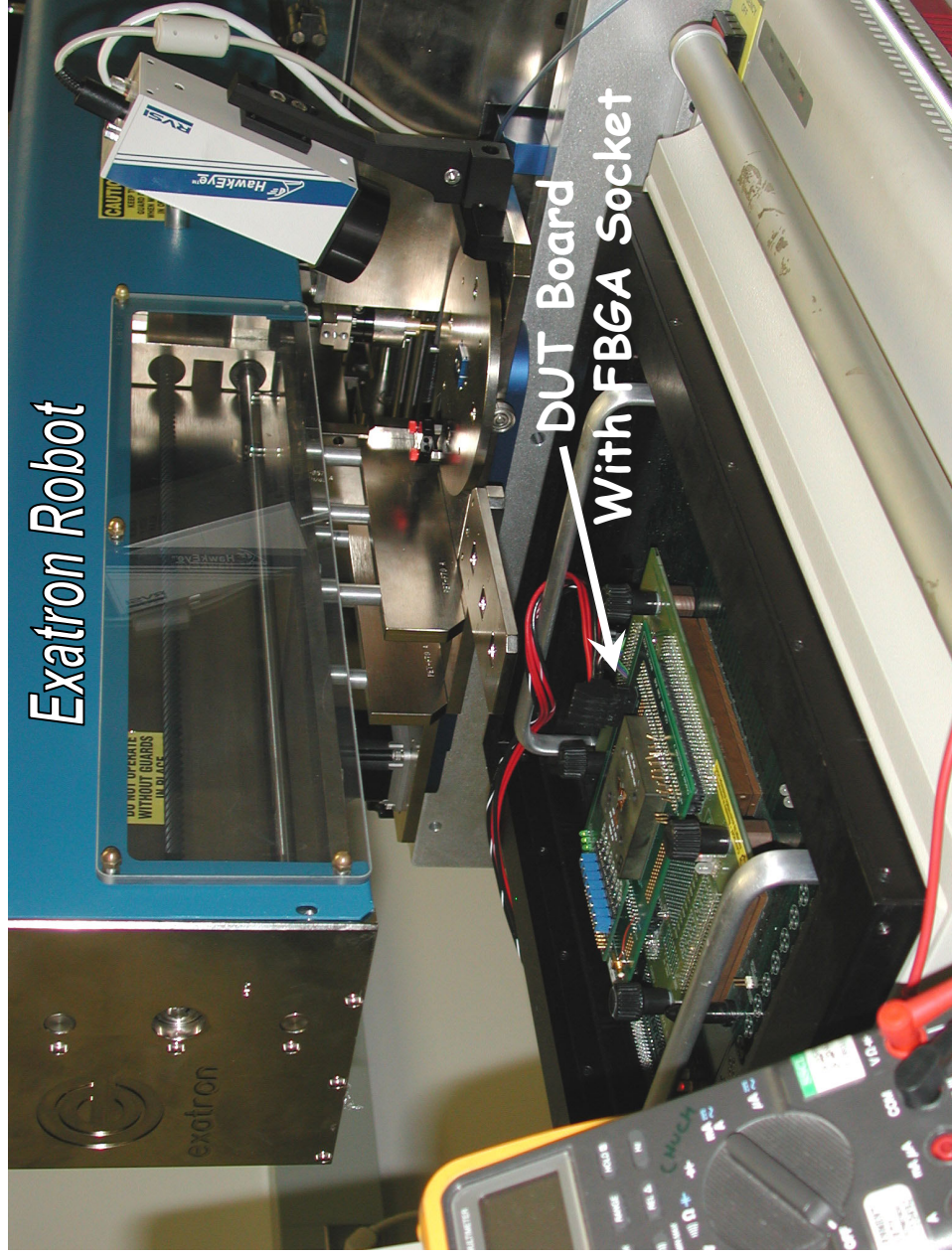


# ASDBLR

# ATLAS TRT

# DUT Board on IMS

# FEE2003



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# IMS Tests on ASDBLR

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- Read Bar code and record test (event) Number
- Supply Current
- Input voltage/resistance
- Output current / switching
- Low Threshold response to 0, 2, 3 fC input
- High Threshold response to 30 fC.

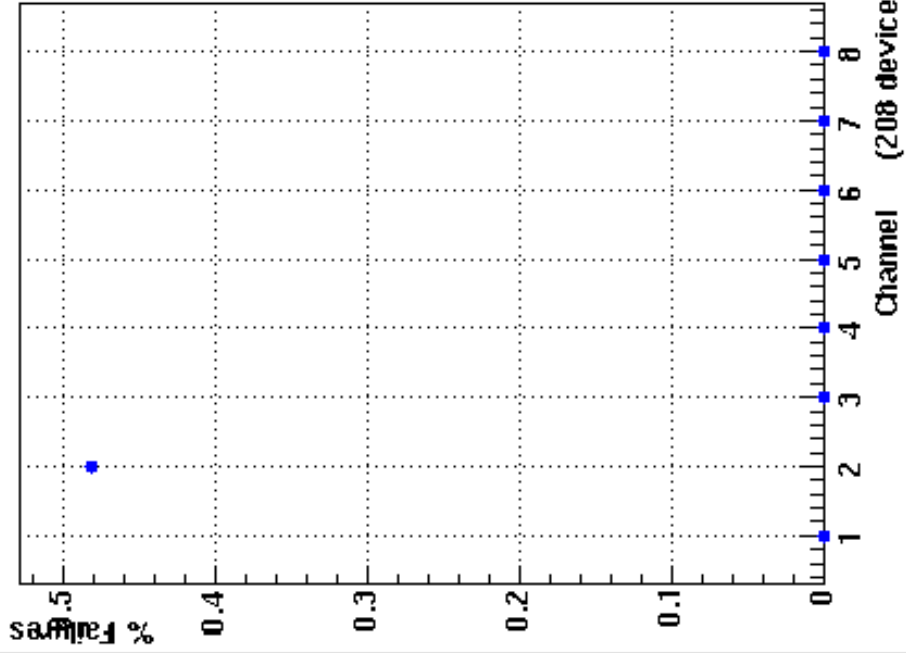
**Write Results to SQL data base**



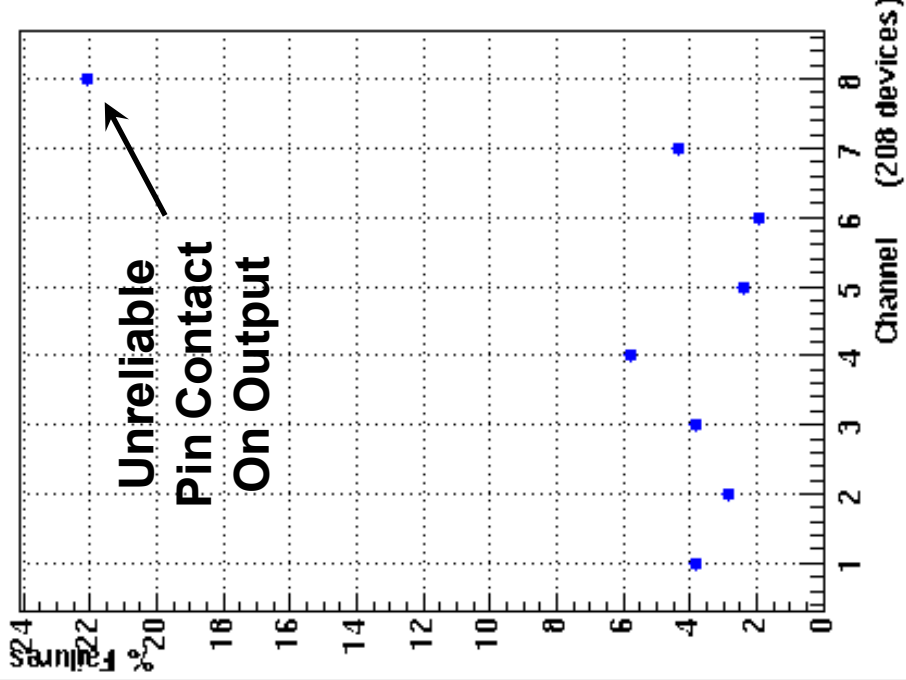
# Failures Due to Socket Pin Reliability

## ATLAS TRT FEE2003

INPUTS, Lot # 125



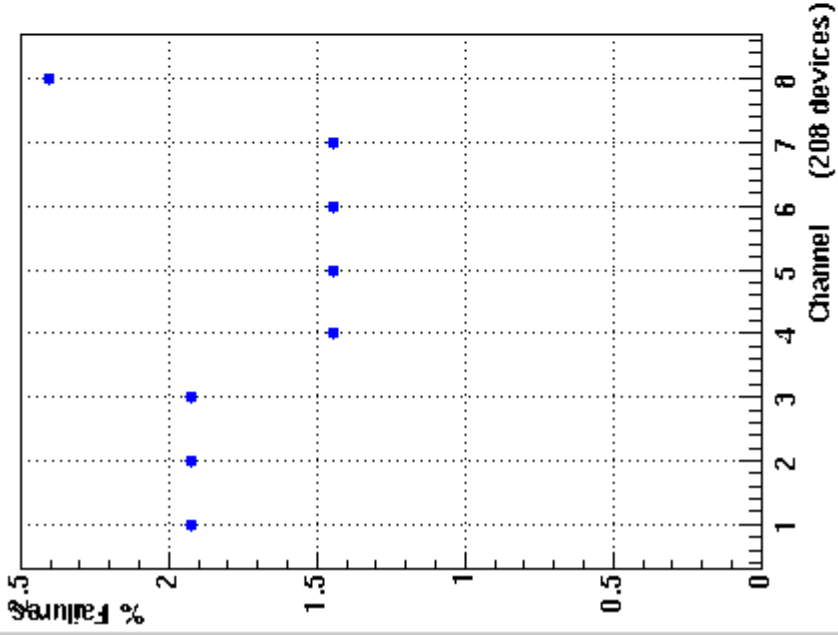
OUTPUTS, Lot # 125



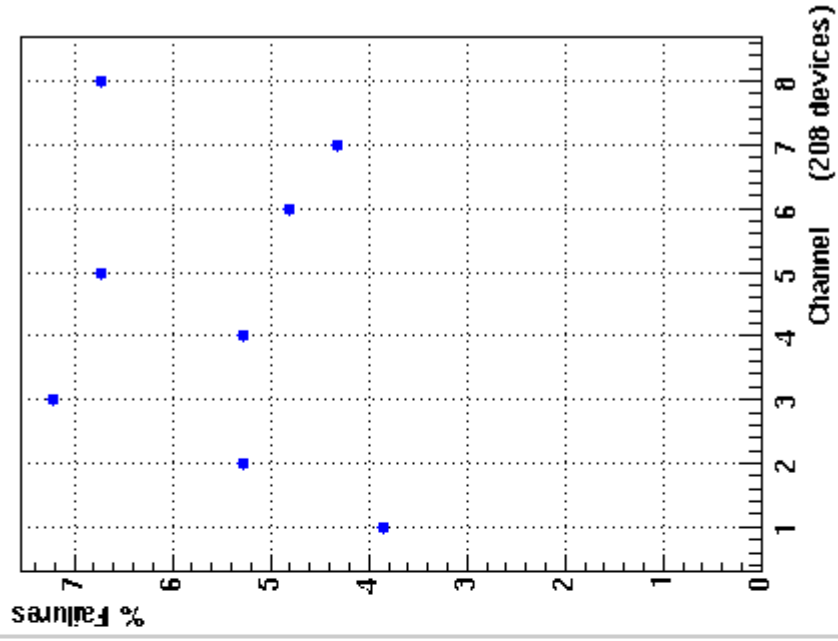
# Using Forced Air to clean pogo pins

# ATLAS TRT FEE2003

INPUTS, Lot # 129



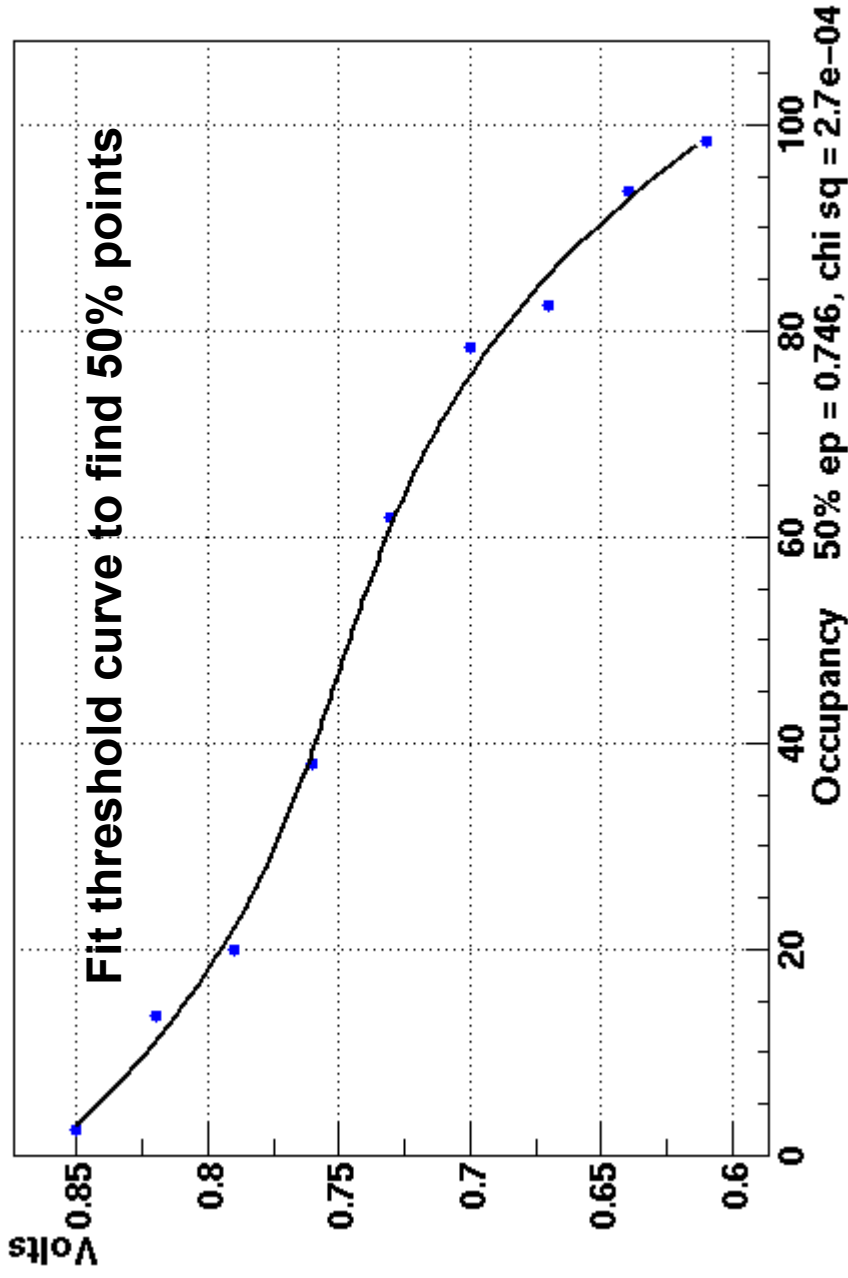
OUTPUTS, Lot # 129



# Finding ASDBLR 50% Threshold

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Q1 TestNum 8633, Ch5, 30mv Sp



# IMS Beta Stage Testing

## Experience

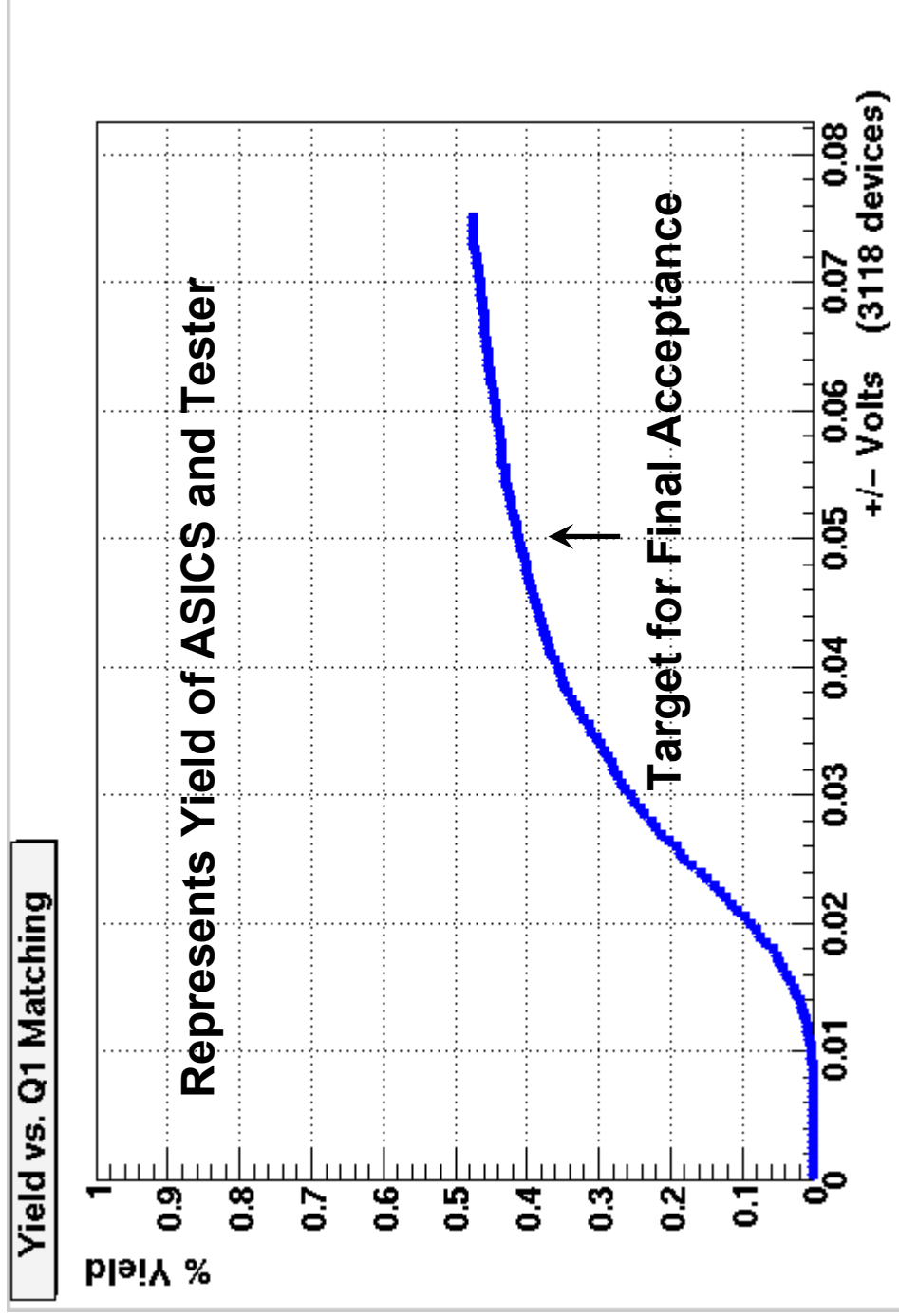
# ATLAS TRT

## FEE2003

- First 3000 chips demonstrate minor problems.
- Socket Pins must be cleared with forced air daily.
- Some wandering of the Threshold 50% points day to day.
- Bar code too close to chip label, leads to ~5% read errors.

**False failure rate ~10% presently**  
**Should improve over time.**

# Yield on First 3000 Devices **ATLAS TRT** with Beta Testing version **FEE2003**

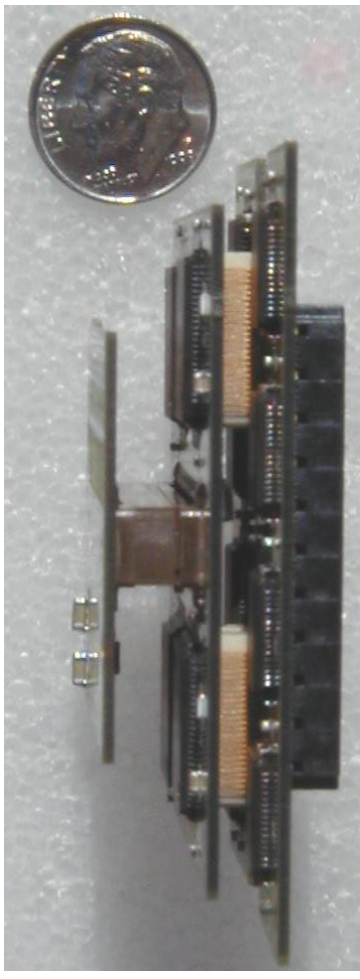


# End Cap Wheel Boards

# ATLAS TRT FEE2003

- 192 channels per assembly
- 2 DTM Board's = 1 virtual module.
  - 1/32 of endcap type A wheel
- Flexible interconnect between 64 channel DTMROC board allows 192 channel board to follow curvature of wheel tread.
- Initial noise measurements on prototype detector show operation at 2fC possible.

Side view of the stackup of one 64 channel ASD board, one (old) 64 channel DTM board, and a connector board

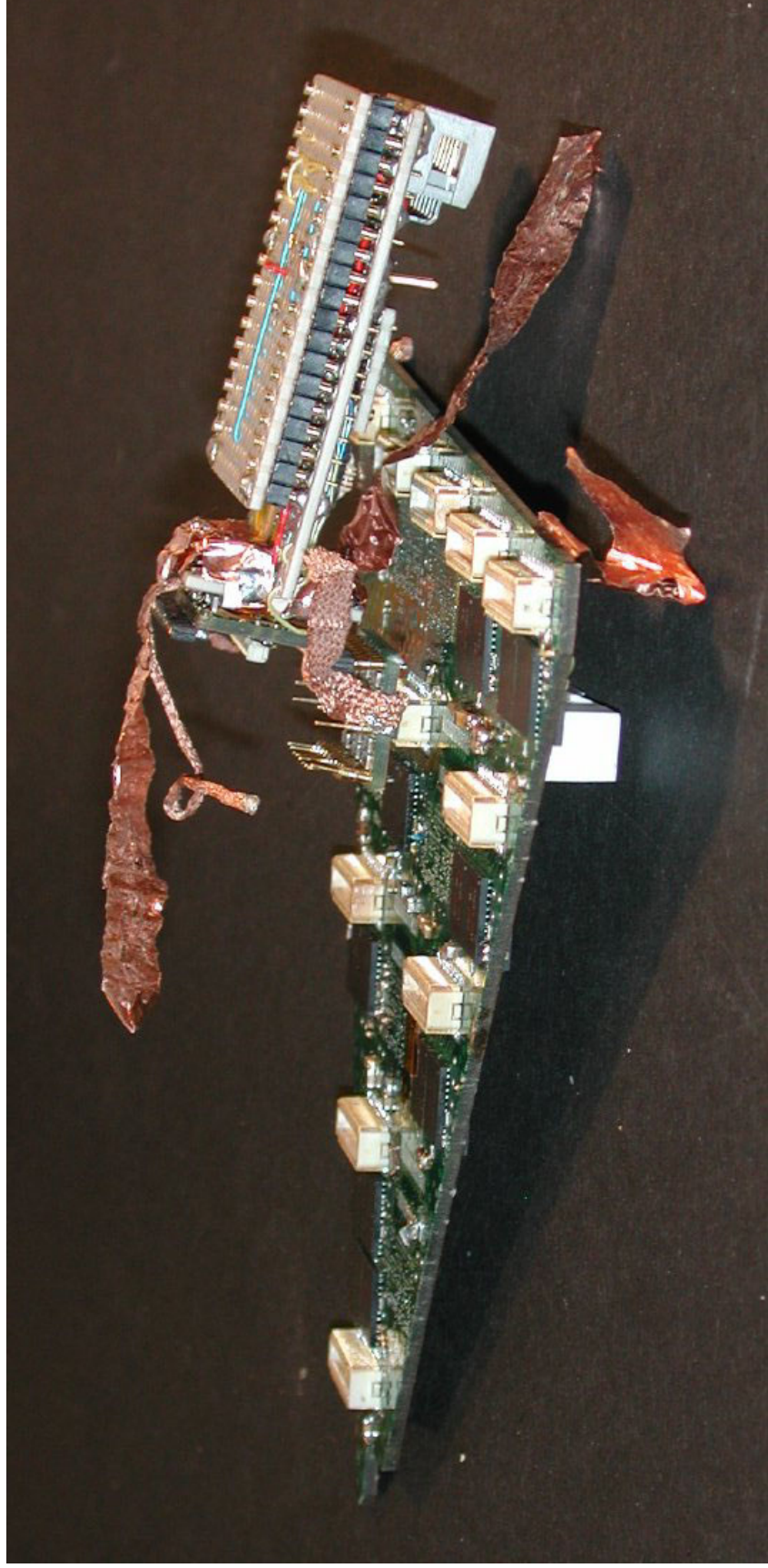


**192 channel DTMROC board**



# Barrel Module Board with 15 ASDBLR / DTMROC triplets

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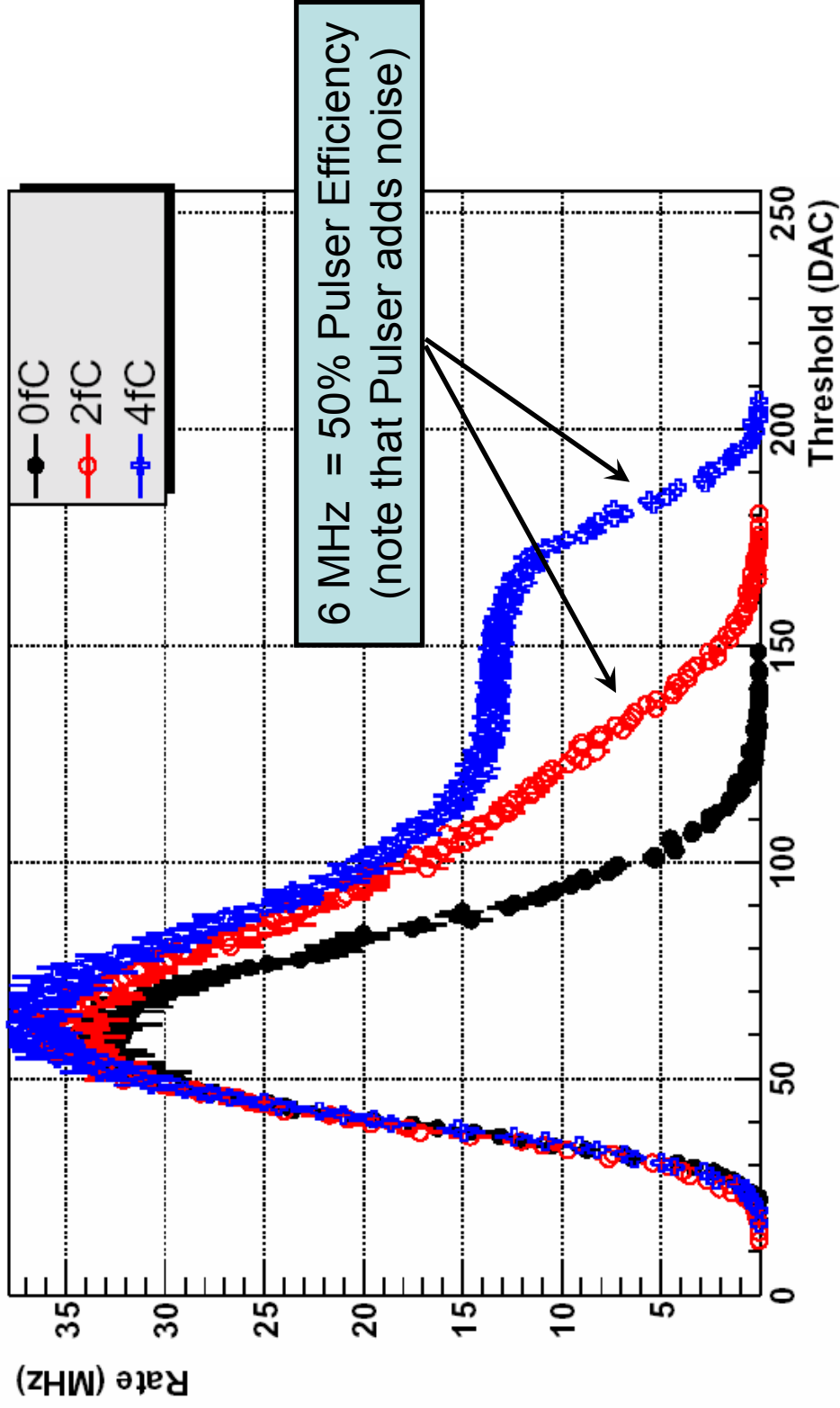


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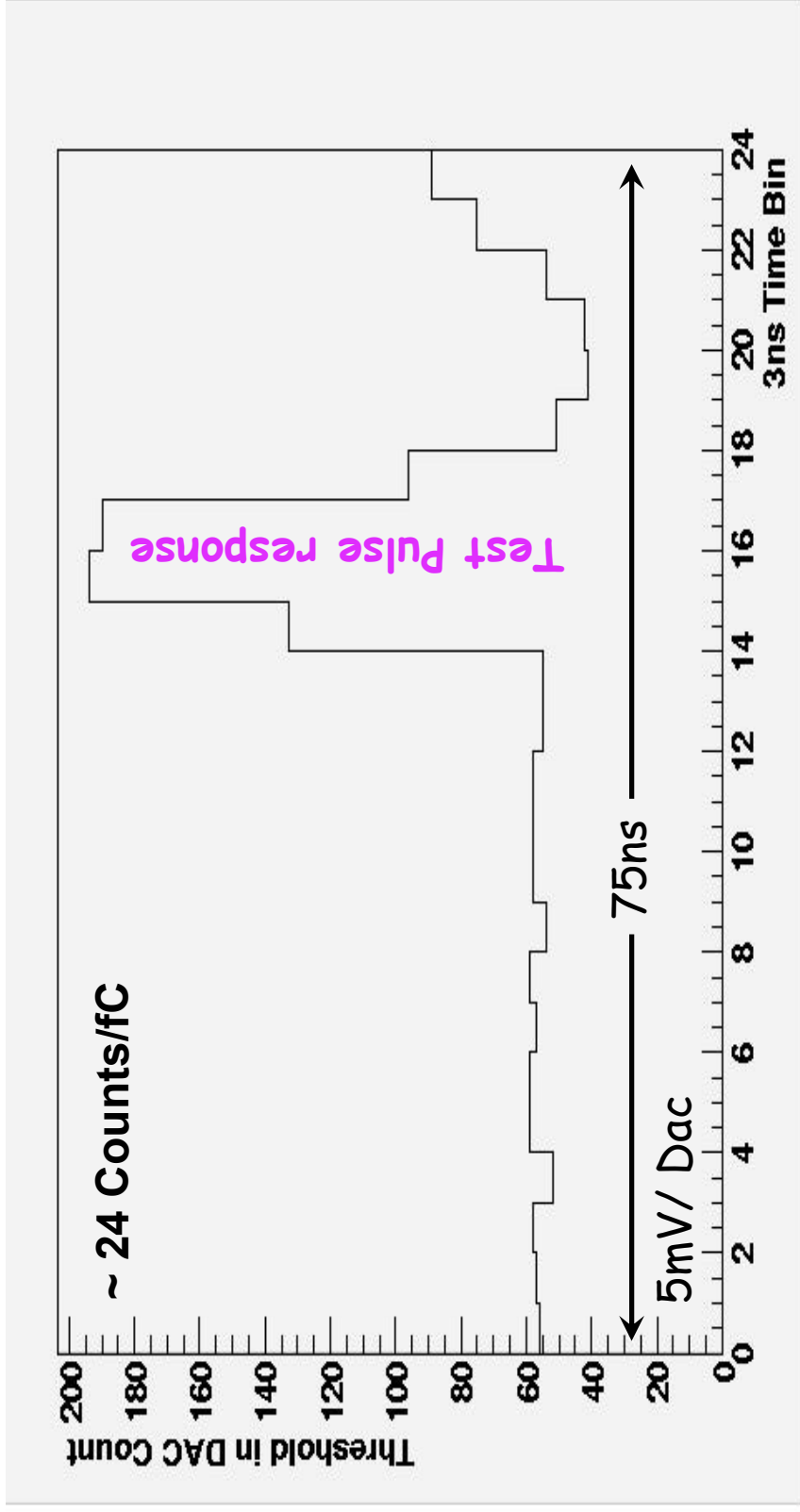
### Noise Rate Plot with Barrel ModuleBoard and Pulser





## Analog and Digital Readout on the Barrel Module Board (good Channel)

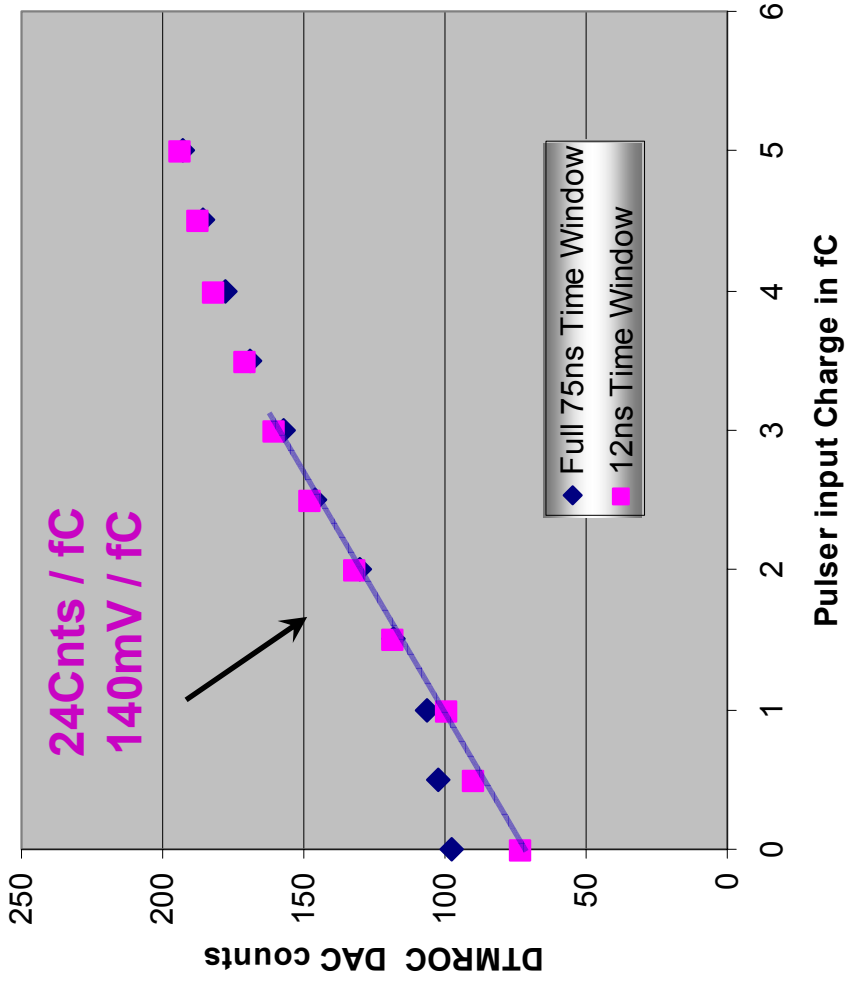
### 50% Efficiency Dac Setting by Time Bin



# Beating Down Pulser Noise using DTMROC Timing window

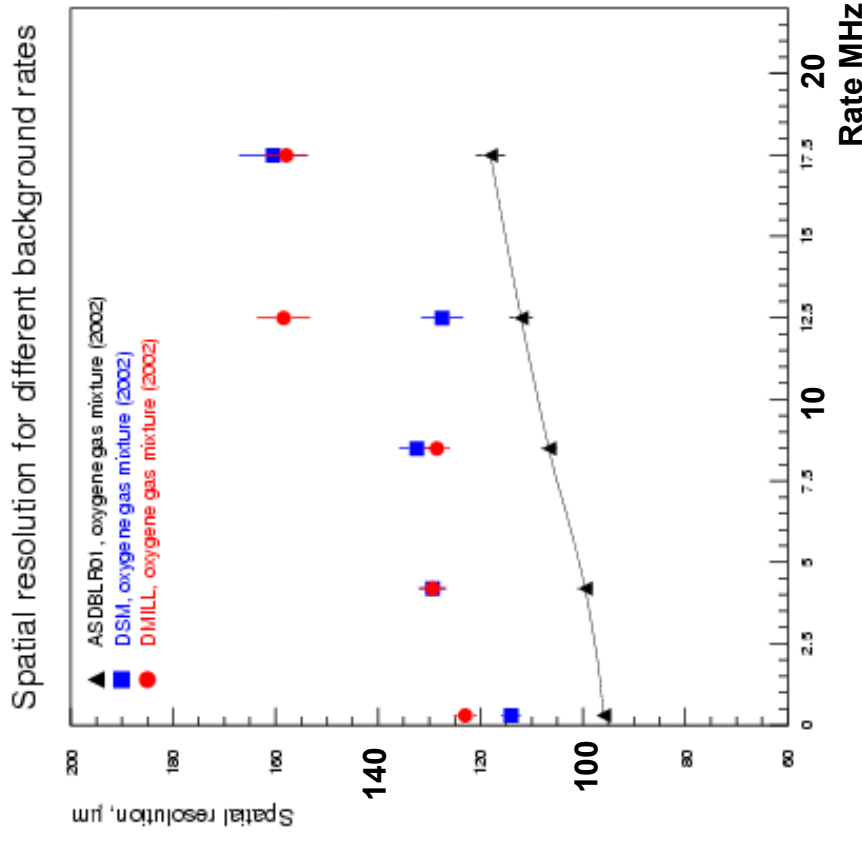
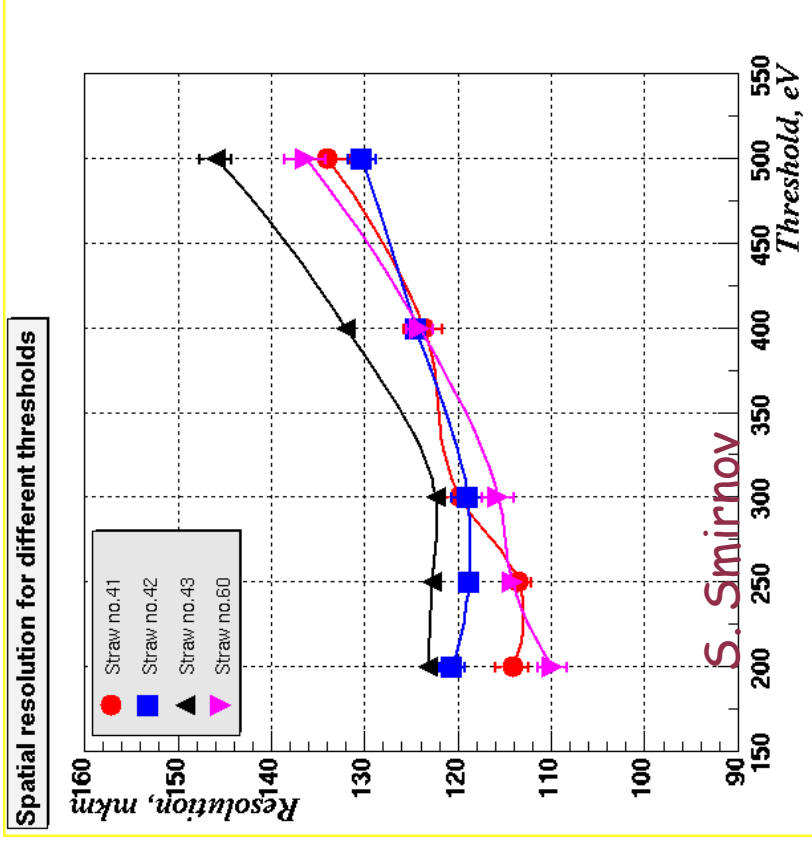
## ATLAS TRT FEE2003

### 50% Threshold VS Input Charge



# Test Beam Measurements Spatial Resolution

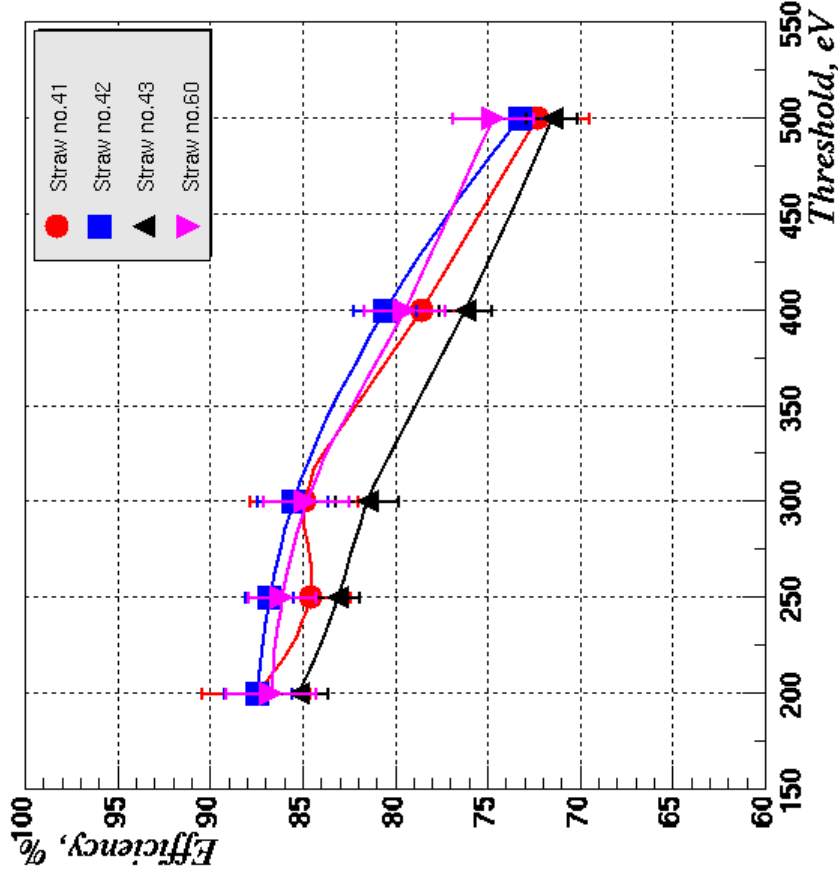
# ATLAS TRT FEE2003



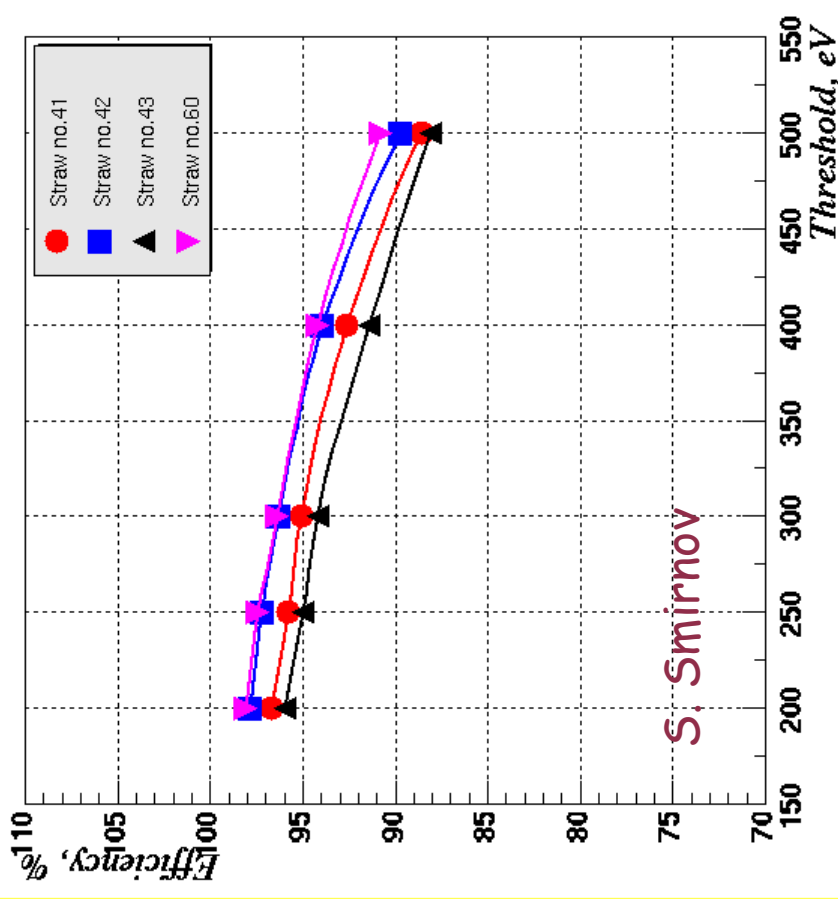
# Test Beam Performance of Production ASICS and near final prototype boards.

## ATLAS TRT FEE2003

2.5-sigma efficiency for different thresholds



Total efficiency for different thresholds



S. Smirnov

# Summary

**ATLAS TRT**  
**FEE2003**

- ASDBLR and DTMROC ASICs are in production and have been shown to meet TRT design objectives.
- Development of Production ASIC Testing Facility is nearly finished.
- Design of Boards with both analog and digital ASICs on them is underway and we have very promising results to date.
- Radiation Testing of ASDBLR ASICs indicates npn neutron sensitivity that may limit lifetime to ~8 years when safety factors are considered.
- Thermal neutron content of TRT environment needs study.